TPS5331x High-Efficiency, 8-A or 14-A, Synchronous Buck Converter with Eco-mode Control

1 Features

- Conversion Input Voltage Range: 1.5 V to 22 V
- VDD Input Voltage Range: 4.5 V to 25 V
- 91% Efficiency from 12 V to 1.5 V at 14 A
- Output Voltage Range: 0.6 V to 5.5 V
- 5-V LDO Output
- Supports Single-Rail Input
- Integrated Power MOSFETs with 8 A (TPS53318) or 14 A (TPS53319) of Continuous Output Current
- Auto-Skip Eco-mode™ for Light-Load Efficiency
- < 110 µA Shut Down Current
- D-CAP™ Mode with Fast Transient Response
- Selectable Switching Frequency from 250 kHz to 1 MHz with External Resistor
- Selectable Auto-Skip or PWM-Only Operation
- Built-in 1% 0.6-V Reference.
- 0.7-ms, 1.4-ms, 2.8-ms and 5.6-ms Selectable Internal Voltage Servo Soft-Start
- Integrated Boost Switch
- Pre-Charged Start-Up Capability
- Adjustable Overcurrent Limit with Thermal Compensation
- Overvoltage, Undervoltage, UVLO and Over-Temperature Protection
- Supports All Ceramic Output Capacitors
- Open-Drain Power Good Indication
- Incorporates NexFET™ Power Block Technology
- 22-Pin QFN (DQP) Package with PowerPAD™

2 Applications

- Server/Storage
- Workstations and Desktops
- Telecommunications Infrastructure

3 Description

The TPS53318 and TPS53319 devices are D-CAP mode, 8-A or 14-A synchronous switchers with integrated MOSFETs. They are designed for ease of use, low external component count, and space-conscious power systems.

These devices feature accurate 1%, 0.6-V reference, and integrated boost switch. A sample of competitive features include: 1.5-V to 22-V wide conversion input voltage range, very low external component count, D-CAP™ mode control for super fast transient, auto-skip mode operation, internal soft-start control, selectable frequency, and no need for compensation.

The conversion input voltage ranges from 1.5 V to 22 V, the supply voltage range is from 4.5 V to 25 V, and the output voltage range is from 0.6 V to 5.5 V.

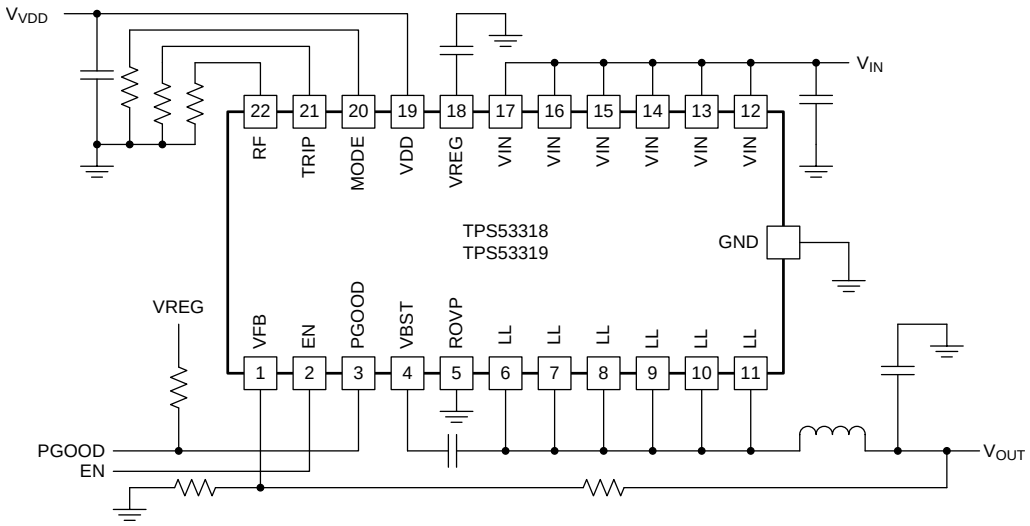
These devices are available in 5 mm x 6 mm, 22-pin QFN package and is specified from –40°C to 85°C.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS53318	LSON-CLIP (22)	6.00 mm x 5.00 mm
TPS53319		

(1) For all available packages, see the *Package Option Addendum* section at the end of the datasheet.

Simplified Application



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

Table of Contents

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (December 2014) to Revision D — **Page**

- Added recommendation for ROVP connection when ROVP function is not needed in *Pin Functions* table ... 3
- Corrected typographical error. Changed "when the VDD voltage rises above 1 V" to "when the VDD voltage rises above 2 V" in the *5-V LDO and VREG Start-Up* section. ... 14
- Added *ROVP Pin Design Note* in *Redundant Overvoltage Protection (OVP)* section ... 17

Changes from Revision B (May 2013) to Revision C — **Page**

- Added *Pin Configuration and Functions* section, *ESD Rating* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section. ... 1
- Added clarity to *Current Sense, Overcurrent and Short Circuit Protection* section ... 16
- Added Table 2 ... 17

Changes from Revision A (JUNE 2012) to Revision B — **Page**

- Added clarity to *Overvoltage and Undervoltage Protection* section ... 17
- Updated Figure 50 ... 28

Changes from Original (JUNE 2012) to Revision A — **Page**

- Changed "< 100 µA Shut Down Current" to "< 110 µA Shut Down Current" in Features ... 1

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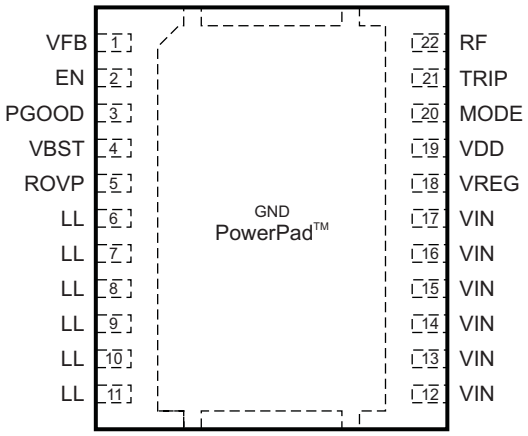
5 Device Comparison Table

ORDER NUMBER(1)	OUTPUT CURRENT (A)
TPS53318DQP	8
TPS53319DQP	14

(1) For detailed ordering information see the *Package Option Addendum* section at the end of this data sheet.

6 Pin Configuration and Functions

DQP (LSON-CLIP) PACKAGE
22 PINS
(TOP VIEW)



Pin Functions

PIN		I/O/P(1)	DESCRIPTION
NAME	NO.		
EN	2	I	Enable pin. Typical turn-on threshold voltage is 1.3 V. Typical turn-off threshold voltage is 1.0 V.
GND		G	Ground and thermal pad of the device. Use proper number of vias to connect to ground plane.
LL	6	B	Output of converted power. Connect this pin to the output inductor.
	7		
	8		
	9		
	10		
	11		
MODE	20	I	Soft-start and mode selection. Connect a resistor to select soft-start time using Table 3. The soft-start time is detected and stored into internal register during start-up.
PGOOD	3	O	Open drain power good flag. Provides 1-ms start-up delay after VFB falls in specified limits. When VFB goes out of the specified limits PGOOD goes low after a 2-µs delay
ROVP	5	I	Redundant overvoltage protection (OVP) input. Use a resistor divider to connect this pin to V_{OUT}. Internally pulled down to GND with 1.5-MΩ resistor. If redundant OVP is not needed, connect this pin to GND or make it float. (See *Redundant Overvoltage Protection (OVP)* section)
RF	22	I	Switching frequency selection. Connect a resistor to GND or VREG to select switching frequency using Table 1. The switching frequency is detected and stored during the startup.
TRIP	21	I	OCL detection threshold setting pin. I_{TRIP} = 10 µA at room temperature, 3000 ppm/°C current is sourced and set the OCL trip voltage as follows.
			$V_{OCL} = V_{TRIP}/32$ ($V_{TRIP} \le 2.4$ V, $V_{OCL} \le 75$ mV)

(1) I = Input, O = Output, B = Bidirectional, P = Supply, G = Ground

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Pin Functions (continued)

PIN		I/O/P[1]	DESCRIPTION
NAME	NO.		
VBST	4	P	Supply input for high-side FET gate driver (boost terminal). Connect capacitor from this pin to LL node. Internally connected to VREG via bootstrap MOSFET switch.
VDD	19	P	Controller power supply input. VDD input voltage range is from 4.5 V to 25 V.
VFB	1	I	Output feedback input. Connect this pin to V_{OUT} through a resistor divider.
VIN	12	P	Conversion power input. The conversion input voltage range is from 1.5 V to 22 V.
	13		
	14		
	15		
	16		
	17		
VREG	18	P	5-V low drop out (LDO) output. Supplies the internal analog circuitry and driver circuitry.
Thermal Pad		G	Ground and thermal pad of the device. Use proper number of vias to connect to ground plane.

7 Specifications

7.1 Absolute Maximum Ratings[1]

			VALUE		UNIT
			MIN	MAX	
Input voltage range	VIN (main supply)		–0.3	30	V
	VDD		–0.3	28	
	VBST		–0.3	32	
	VBST (with respect to LL)		–0.3	7	
	EN, MODE, TRIP, RF, ROVP, VFB		–0.3	7	
Output voltage range	LL	DC	–2	30	V
		Pulse < 20ns, E = 5 µJ	–7	32	
	PGOOD, VREG		–0.3	7	
	GND		–0.3	0.3	
Source/Sink current	VBST		50		mA
Operating free-air temperature, T_A			–40	85	°C
Junction temperature range, T_J			–40	150	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds				300	
Storage temperature, T_{stg}			–55	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions. Pins listed as ±2000 V may actually have higher performance.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions. Pins listed as ±500 V may actually have higher performance.

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7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Input voltage range	VIN (main supply)	1.5	22	V
	VDD	4.5	25	
	VBST	4.5	28	
	VBST (with respect to LL)	4.5	6.5	
	EN, MODE, TRIP, RF, ROVP, VFB	–0.1	6.5	
Output voltage range	LL	–1	27	V
	PGOOD, VREG	–0.1	6.5	
Junction temperature range, T_J		–40	125	°C

7.4 Thermal Information

THERMAL METRIC[1]		TPS53318 TPS53319 DQP 22 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	27.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	17.1	
$R_{\theta JB}$	Junction-to-board thermal resistance	5.9	
ψ_{JT}	Junction-to-top characterization parameter	0.8	
ψ_{JB}	Junction-to-board characterization parameter	5.8	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.2	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

7.5 Electrical Characteristics

Over recommended free-air temperature range, V_{VDD} = 12 V (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
V_{VIN}	VIN pin power conversion input voltage		1.5		22	V
V_{VDD}	Supply input voltage		4.5		25.0	V
$I_{VIN(leak)}$	VIN pin leakage current	V_{EN} = 0 V			1	µA
I_{VDD}	VDD supply current	T_A = 25°C, No load, V_{EN} = 5 V, V_{VFB} = 0.630 V		420	590	µA
I_{VDDSDN}	VDD shutdown current	T_A = 25°C, No load, V_{EN} = 0 V			110	µA
INTERNAL REFERENCE VOLTAGE						
V_{VFB}	VFB regulation voltage	CCM condition[1]		0.600		V
V_{VFB}	VFB regulation voltage	T_A = 25°C	0.597	0.600	0.603	V
		0°C ≤ T_A ≤ 85°C	0.5952	0.600	0.6048	
		–40°C ≤ T_A ≤ 85°C	0.594	0.600	0.606	
I_{VFB}	VFB input current	V_{VFB} = 0.630 V, T_A = 25°C		0.01	0.20	µA
LDO OUTPUT						
V_{VREG}	LDO output voltage	0 mA ≤ I_{VREG} ≤ 30 mA	4.77	5.00	5.36	V
I_{VREG}	LDO output current[1]	Maximum current allowed from LDO			30	mA
V_{DO}	Low drop out voltage	V_{VDD} = 4.5 V, I_{VREG} = 30 mA			250	mV
BOOT STRAP SWITCH						
V_{FBST}	Forward voltage	$V_{VREG-VBST}$, I_F = 10 mA, T_A = 25°C		0.1	0.2	V
I_{VBSTLK}	VBST leakage current	V_{VBST} = 23 V, V_{SW} = 17 V, T_A = 25°C		0.01	1.50	µA

(1) Ensured by design. Not production tested.

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Electrical Characteristics (continued)

Over recommended free-air temperature range, V_{VDD} = 12 V (unless otherwise noted)

PARAMETER			CONDITIONS	MIN	TYP	MAX	UNIT
DUTY AND FREQUENCY CONTROL							
$t_{OFF(min)}$	Minimum off-time		T_A = 25°C	150	260	400	ns
$t_{ON(min)}$	Minimum on-time		V_{IN} = 17 V, V_{OUT} = 0.6 V, f_{SW} = 1 MHz, T_A = 25 °C(1)		35		ns
SOFT-START TIMING							
t_{SS}	Internal soft-start time from V_{OUT} = 0 V to 95% of V_{OUT}		R_{MODE} = 39 kΩ		0.7		ms
			R_{MODE} = 100 kΩ		1.4		
			R_{MODE} = 200 kΩ		2.8		
			R_{MODE} = 470 kΩ		5.6		
OUTPUT VOLTAGE DISCHARGE							
I_{DSCHG}	Output voltage discharge current		V_{EN} = 0 V, V_{SW} = 0.5 V	5.0	6.6	9.0	mA
POWERGOOD							
V_{THPG}	PG threshold		PG in from lower	92.5%	95.0%	98.5%	
			PG in from higher	107.5%	110.0%	112.5%	
			PG hysteresis	2.5%	5.0%	7.5%	
R_{PG}	PG transistor on-resistance			15	30	60	Ω
t_{PGDEL}	PG delay		Delay for PG in	0.8	1	1.2	ms
LOGIC THRESHOLD AND SETTING CONDITIONS							
V_{EN}	EN Voltage		Enable	1.0	1.3	1.6	V
			Disable	0.8	1.0	1.2	
I_{EN}	EN Input current		V_{EN} = 5 V			1.0	µA
f_{SW}	Switching frequency		R_{RF} = 0 Ω to GND, T_A = 25°C(2)	200	250	300	kHz
			R_{RF} = 187 kΩ to GND, T_A = 25°C(2)	250	300	350	
			R_{RF} = 619 kΩ, to GND, T_A = 25°C(2)	350	400	450	
			R_{RF} = Open, T_A = 25°C(2)	450	500	550	
			R_{RF} = 866 kΩ to VREG, T_A = 25°C(2)	540	600	660	
			R_{RF} = 309 kΩ to VREG, T_A = 25°C(2)	670	750	820	
			R_{RF} = 124 kΩ to VREG, T_A = 25°C(2)	770	850	930	
			R_{RF} = 0 Ω to VREG, T_A = 25°C(2)	880	970	1070	
PROTECTION: CURRENT SENSE							
I_{TRIP}	TRIP source current		V_{TRIP} = 1 V, T_A = 25°C		10		µA
TC_{ITRIP}	TRIP current temperature coefficient		On the basis of 25°C(2)		3000		ppm/°C
V_{TRIP}	Current limit threshold setting range	TPS53318	$V_{TRIP-GND}$	0.4		1.5	V
		TPS53319				2.4	
V_{OCL}	Current limit threshold		V_{TRIP} = 1.2 V	37.5			mV
			V_{TRIP} = 0.4		12.5		
V_{OCLN}	Negative current limit threshold		V_{TRIP} = 1.2 V		–37.5		mV
			V_{TRIP} = 0.4 V		–12.5		
I_{OCP}	Valley current limit threshold		R_{TRIP} = 66.5 kΩ, 0°C ≤ T_A ≤ 125°C	4.6	5.4	6.3	A
			R_{TRIP} = 66.5 kΩ, –40°C ≤ T_A ≤ 125°C	4.4	5.4	6.3	
V_{AZCADJ}	Auto zero cross adjustable range		Positive	3	15		mV
			Negative		–15	–3	

(2) Not production tested. Test condition is V_{IN} = 12 V, V_{OUT} = 1.2 V, I_{OUT} = 5 A using application circuit shown in Figure 45.

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Electrical Characteristics (continued)

Over recommended free-air temperature range, V_{VDD} = 12 V (unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
PROTECTION: UVP and OVP						
V_{OVP}	OVP trip threshold	OVP detect	115%	120%	125%	
t_{OVPDEL}	OVP propagation delay	VFB delay with 50-mV overdrive		1		µs
V_{UVP}	Output UVP trip threshold	UVP detect	65%	70%	75%	
t_{UVPDEL}	Output UVP propagation delay		0.8	1.0	1.2	ms
t_{UVPEN}	Output UVP enable delay	From enable to UVP workable	1.5	2.3	3.0	ms
UVLO						
V_{UVVREG}	VREG UVLO threshold	Wake up	4.00	4.20	4.33	V
		Hysteresis		0.25		
PROTECTION: UVP and OVP						
V_{OVP}	OVP trip threshold	OVP detect	115%	120%	125%	
t_{OVPDEL}	OVP propagation delay	VFB delay with 50-mV overdrive		1		µs
V_{UVP}	Output UVP trip threshold	UVP detect	65%	70%	75%	
t_{UVPDEL}	Output UVP proprogation delay		0.8	1.0	1.2	ms
t_{UVPEN}	Output UVP enable delay	From enable to UVP workable	1.5	2.3	3.0	ms
UVLO						
V_{UVVREG}	VREG UVLO threshold	Wake up	4.00	4.20	4.33	V
		Hysteresis		0.25		
THERMAL SHUTDOWN						
T_{SDN}	Thermal shutdown threshold	Shutdown temperature (2)		145		°C
		Hysteresis (2)		10		

7.6 Typical Characteristics

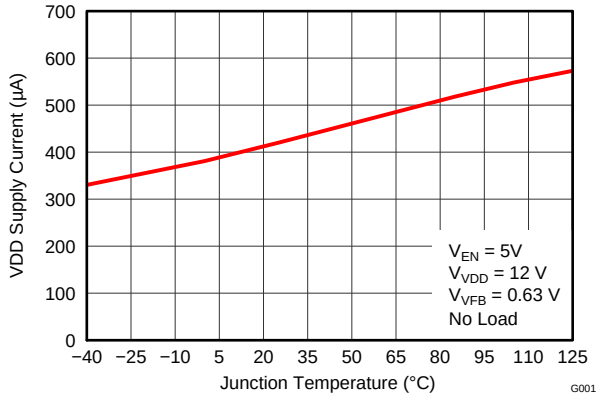

Figure 1. VDD Supply Current vs. Junction Temperature

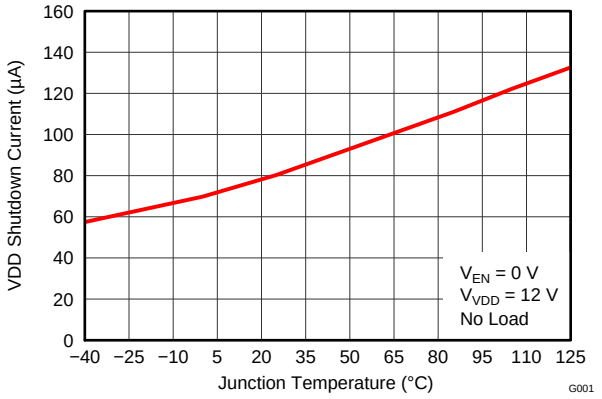

Figure 2. VDD Shutdown Current vs. Junction Temperature

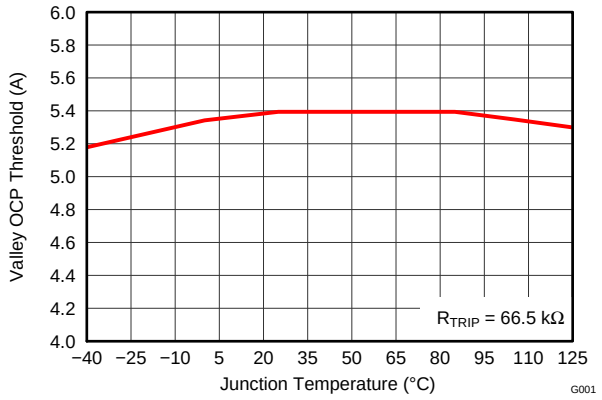

Figure 3. Valley OCP Threshold vs Temperature

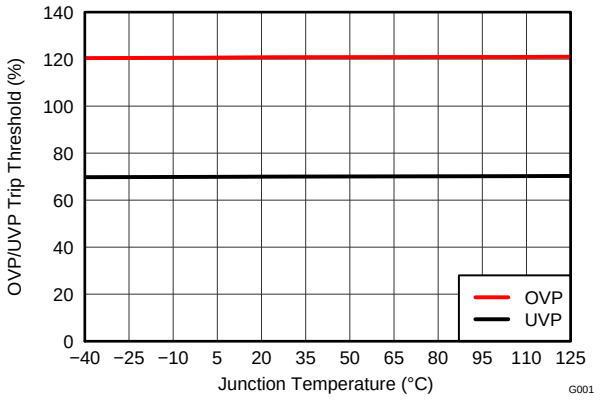

Figure 4. OVP/UVP Trip Threshold vs. Junction Temperature

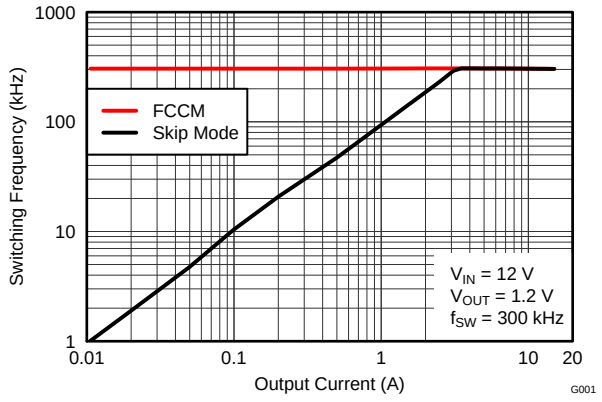

Figure 5. Switching Frequency vs. Output Current

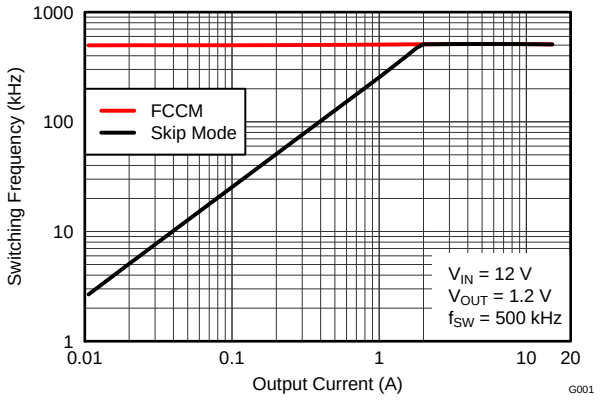

Figure 6. Switching Frequency vs. Output Current

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Typical Characteristics (continued)

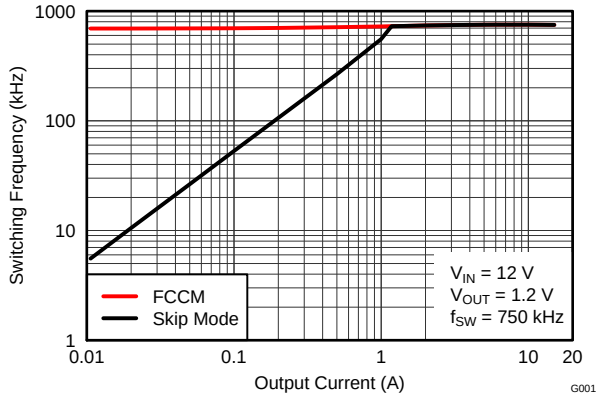

Figure 7. Switching Frequency vs. Output Current

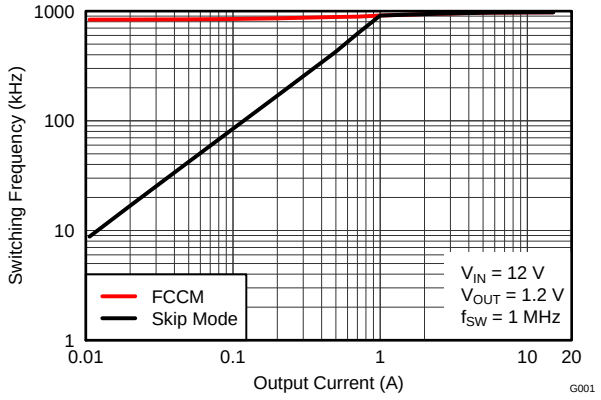

Figure 8. Switching Frequency vs. Output Current

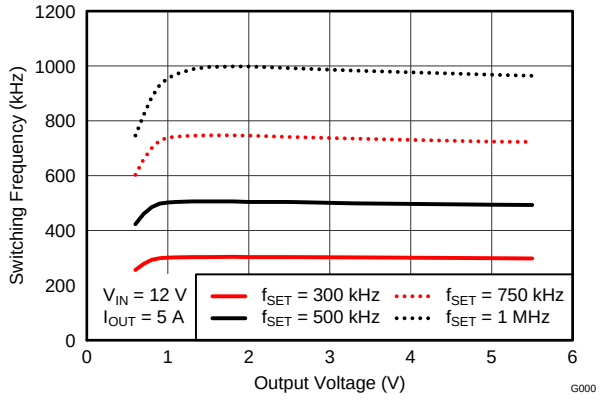

Figure 9. Switching Frequency vs. Output Voltage

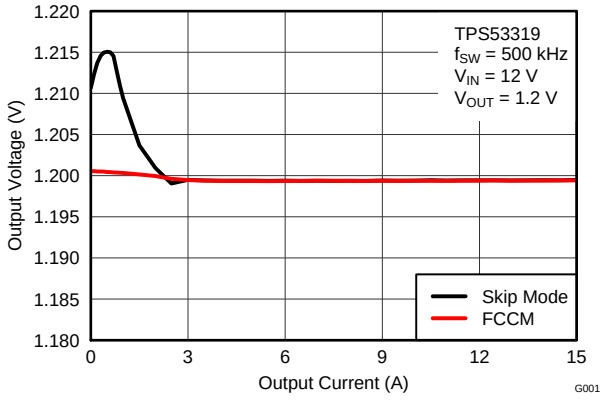

Figure 10. Output Voltage vs. Output Current

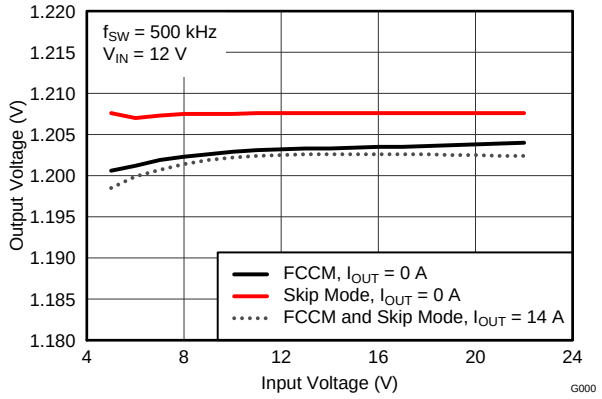

Figure 11. Output Voltage vs. Input Voltage

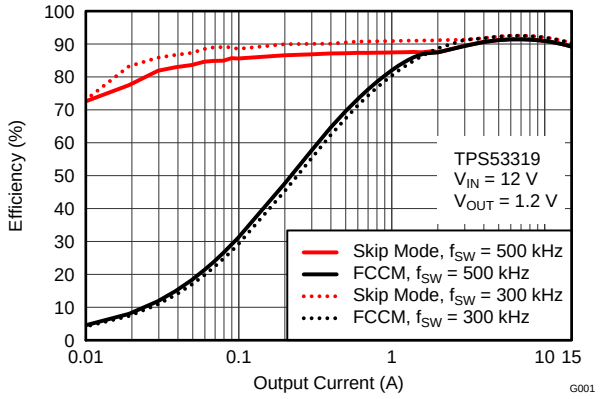

Figure 12. Efficiency vs Output Current

Typical Characteristics (continued)

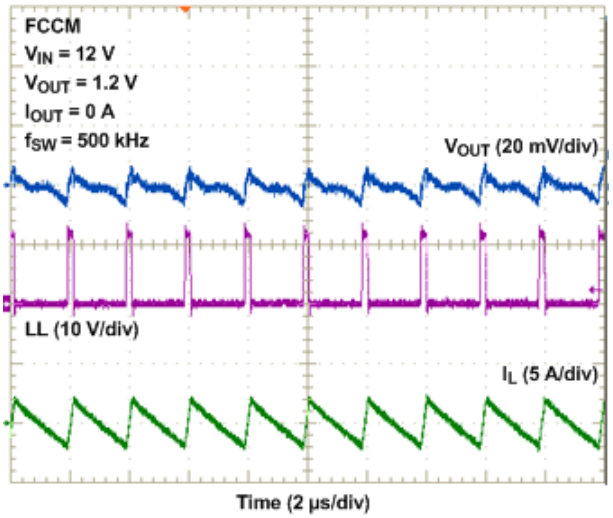

Figure 13. 1.2-V Output FCCM Mode Steady-State Operation

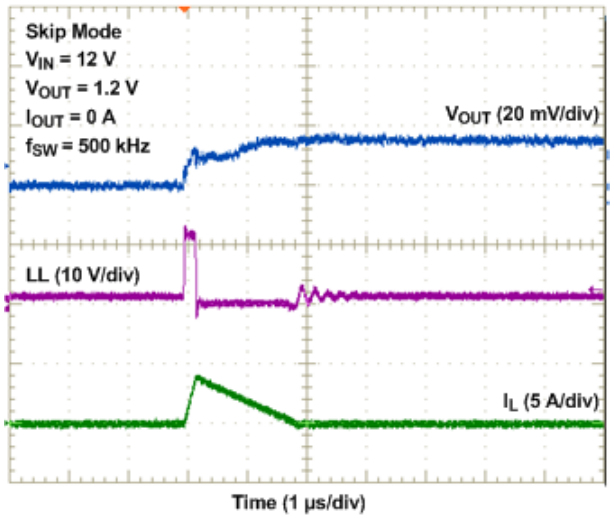

Figure 14. 1.2-V Output Skip Mode Steady-State Operation

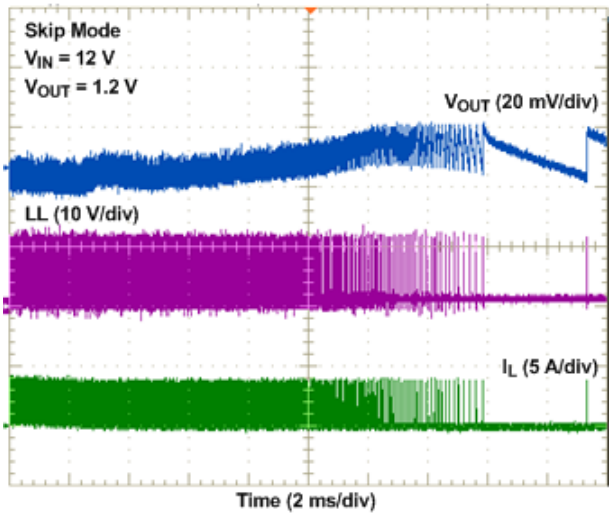

Figure 15. CCM to DCM Transition

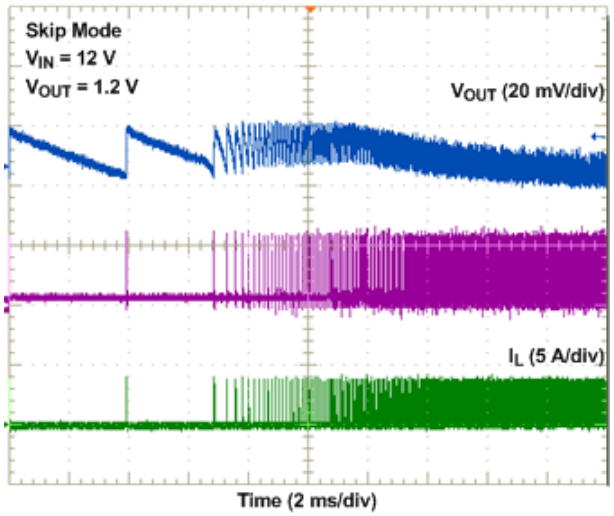

Figure 16. DCM to CCM Transition

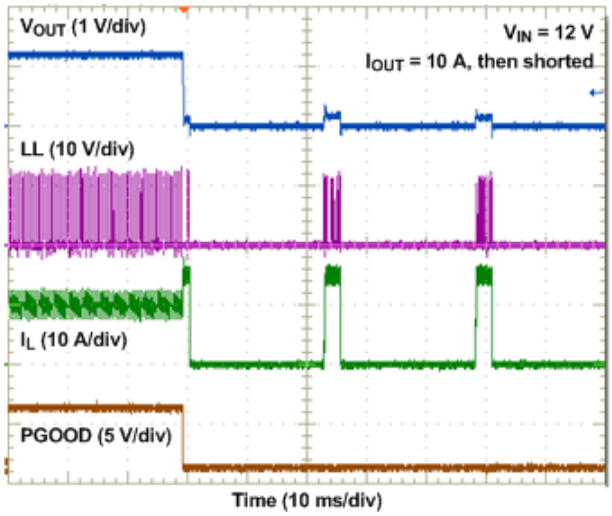

Figure 17. Short Circuit Protection

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7.7 TPS53319 Typical Characteristics

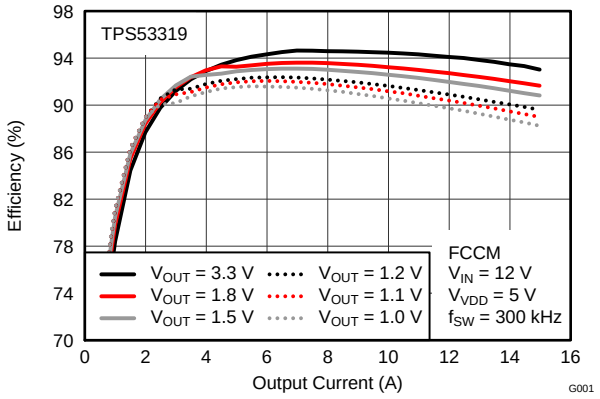

Figure 18. Efficiency vs Output Current

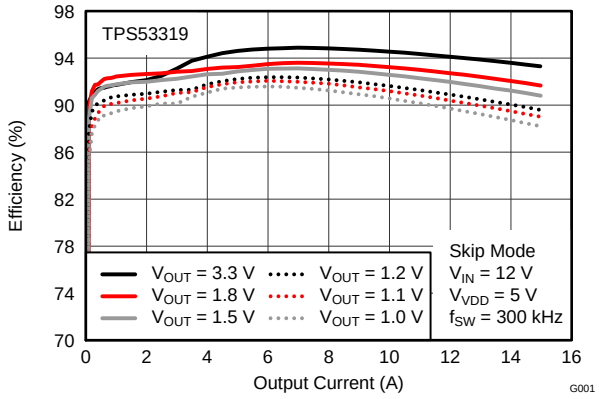

Figure 19. Efficiency vs Output Current

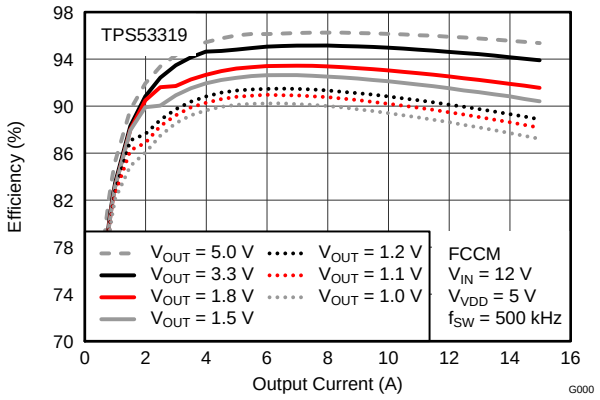

Figure 20. Efficiency vs Output Current

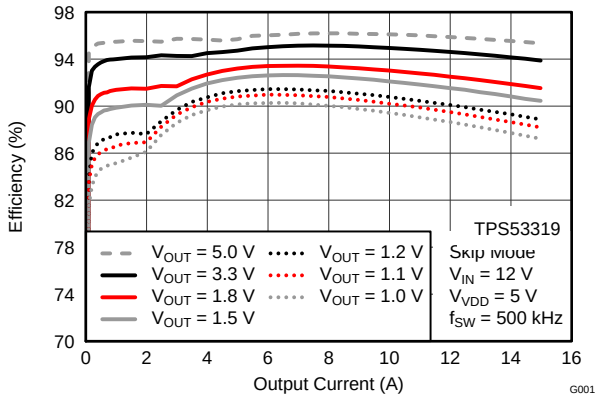

Figure 21. Efficiency vs Output Current

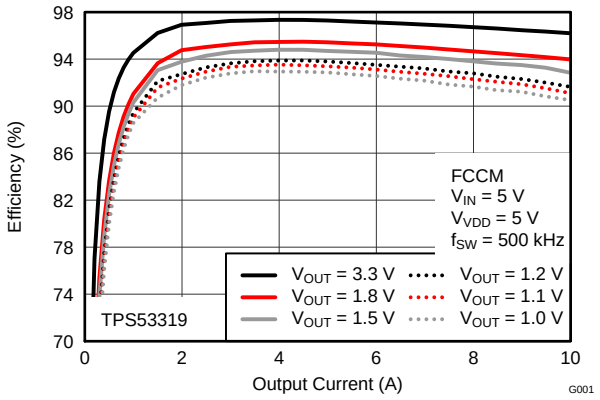

Figure 22. Efficiency vs Output Current

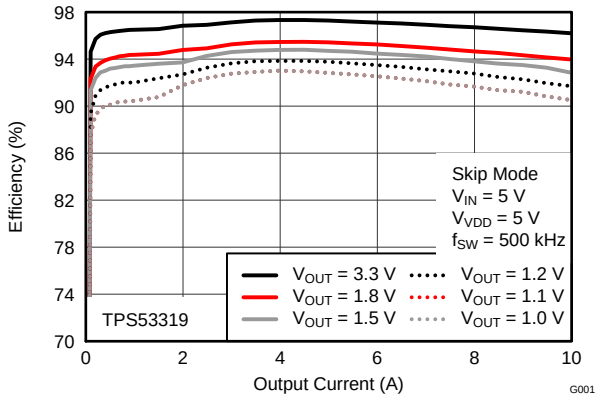

Figure 23. Efficiency vs Output Current

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7.8 TPS53318 Typical Characteristics

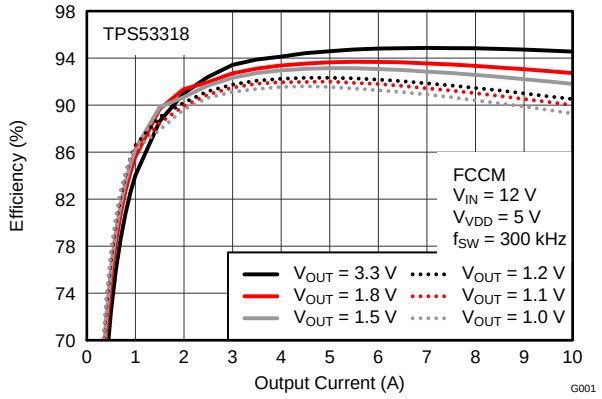

Figure 24. Efficiency vs Output Current

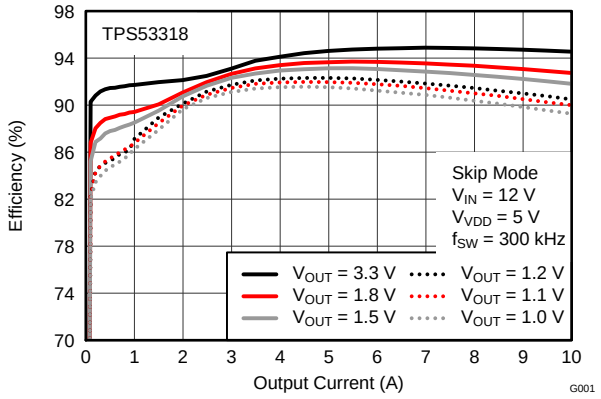

Figure 25. Efficiency vs Output Current

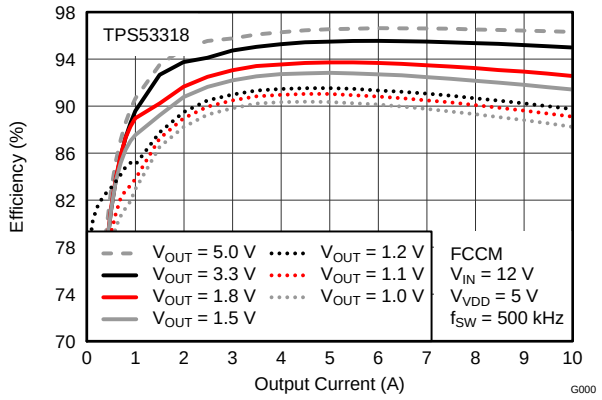

Figure 26. Efficiency vs Output Current

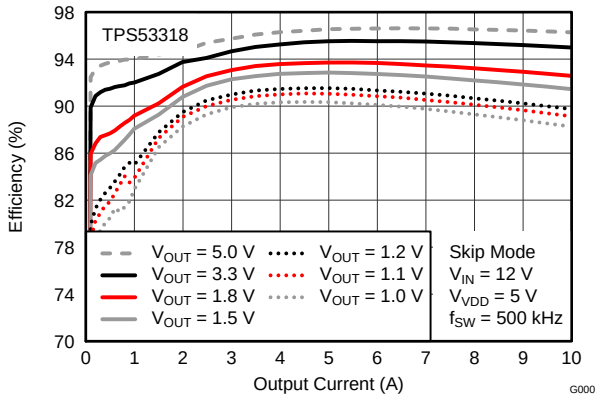

Figure 27. Efficiency vs Output Current

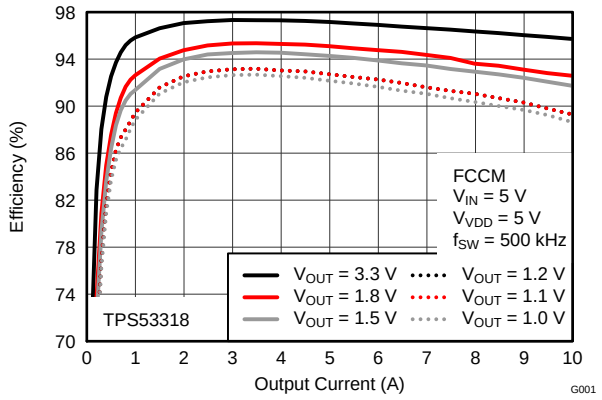

Figure 28. Efficiency vs Output Current

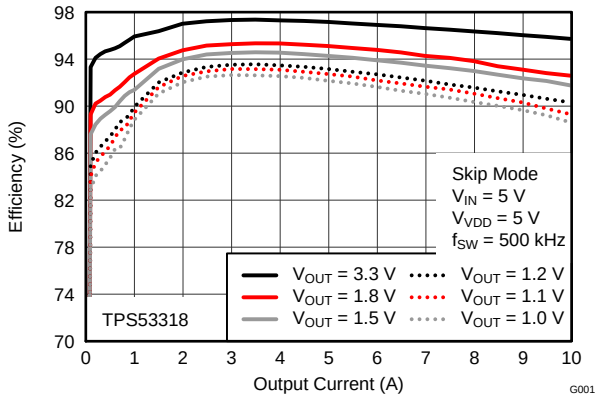

Figure 29. Efficiency vs Output Current

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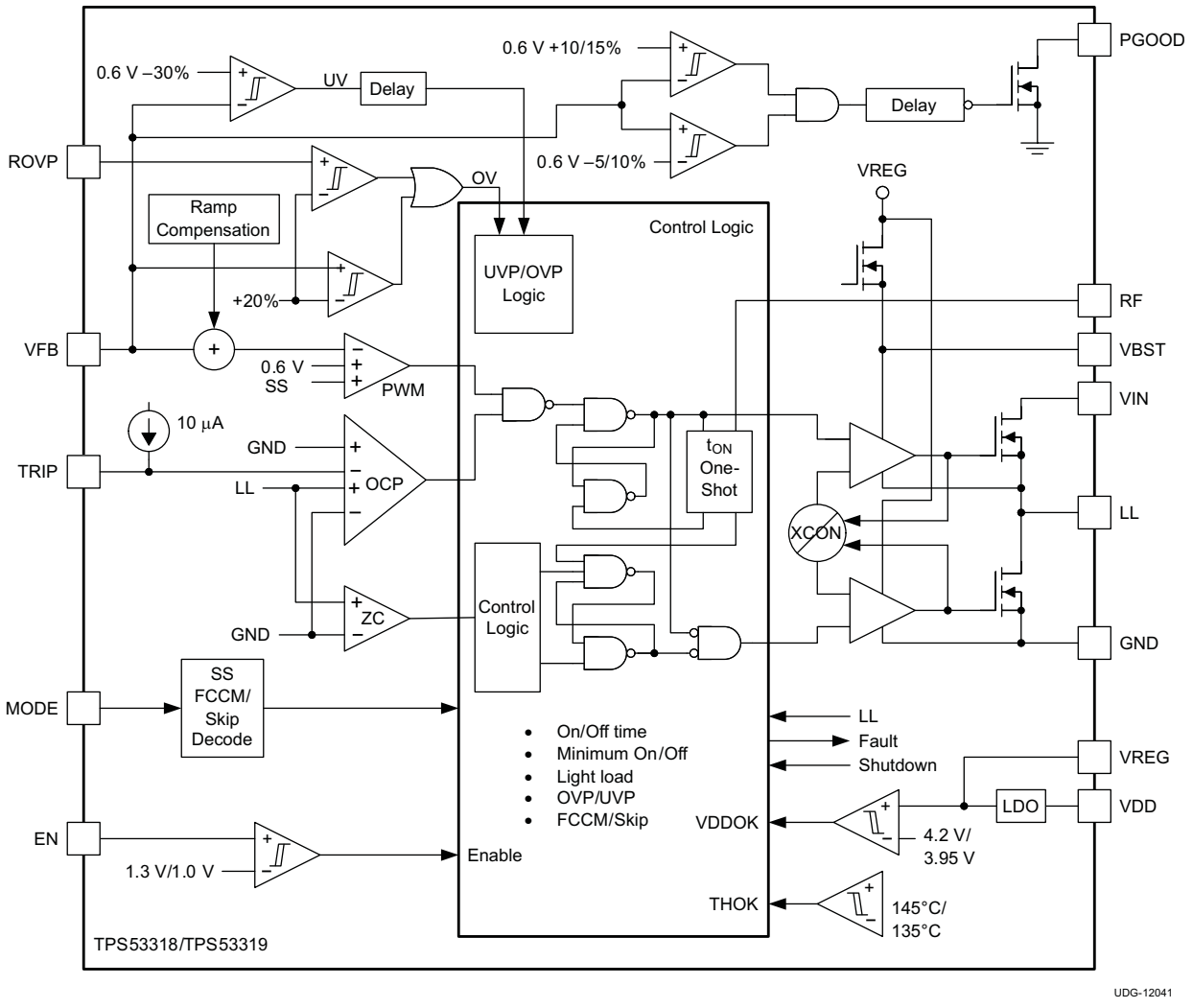
8 Detailed Description

8.1 Overview

The TPS53318 and TPS53319 devices are high-efficiency, single channel, synchronous buck converters suitable for low output voltage point-of-load applications in computing and similar digital consumer applications. The device features proprietary D-CAP™ mode control combined with an adaptive on-time architecture. This combination is ideal for building modern low duty ratio, ultra-fast load step response DC-DC converters. The output voltage ranges from 0.6 V to 5.5 V. The conversion input voltage range is from 1.5 V to 22 V and the VDD bias voltage is from 4.5 V to 25 V. The D-CAP™ mode uses the equivalent series resistance (ESR) of the output capacitor(s) to sense the device current. One advantage of this control scheme is that it does not require an external phase compensation network. This allows a simple design with a low external component count. Eight preset switching frequency values can be chosen using a resistor connected from the RF pin to ground or VREG. Adaptive on-time control tracks the preset switching frequency over a wide input and output voltage range while allowing the switching frequency to increase at the step-up of the load.

These devices have a MODE pin to select between auto-skip mode and forced continuous conduction mode (FCCM) for light load conditions. The MODE pin also sets the selectable soft-start time ranging from 0.7 ms to 5.6 ms as shown in Table 3.

8.2 Functional Block Diagram



(1) The thresholds shown in the *Functional Block Diagram* are typical values. Refer to the *Electrical Characteristics* table for threshold tolerance specifications.

8.3 Feature Description

8.3.1 5-V LDO and VREG Start-Up

Both the TPS53318 and TPS53319 devices provide an internal 5-V LDO function using input from VDD and output to VREG. When the VDD voltage rises above 2 V, the internal LDO is enabled and outputs voltage to the VREG pin. The VREG voltage provides the bias voltage for the internal analog circuitry and also provides the supply voltage for the gate drives.

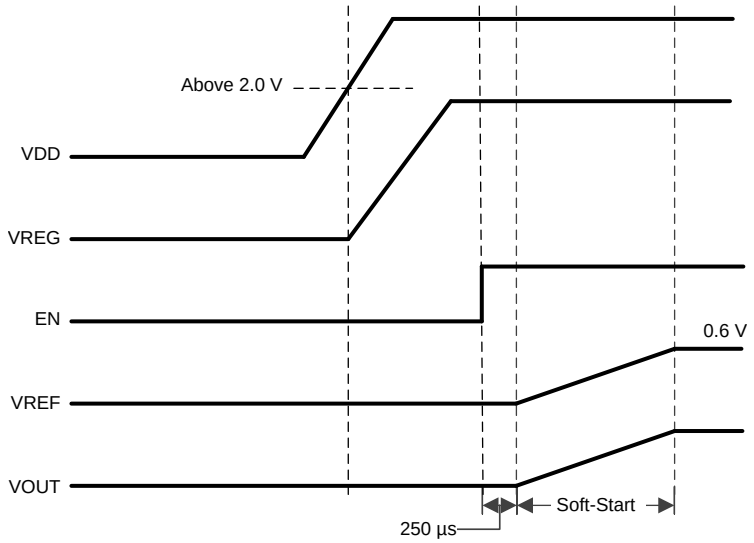


Figure 30. Power-Up Sequence Voltage Waveforms

NOTE

The 5-V LDO is not controlled by the EN pin. The LDO starts-up any time VDD rises to approximately 2 V. (see Figure 30).

8.3.2 Adaptive On-Time D-CAP™ Control and Frequency Selection

Neither the TPS53318 nor the TPS53319 device has a dedicated oscillator to determine switching frequency. However, the device operates with pseudo-constant frequency by feed-forwarding the input and output voltages into the on-time one-shot timer. The adaptive on-time control adjusts the on-time to be inversely proportional to the input voltage and proportional to the output voltage as shown in Equation 1.

$$t_{ON} \propto \frac{V_{OUT}}{V_{IN}} \quad (1)$$

This makes the switching frequency fairly constant in steady state conditions over a wide input voltage range. The switching frequency is selectable from eight preset values by a resistor connected between the RF pin and GND or between the RF pin and the VREG pin as shown in Table 1. Maintaining open resistance sets the switching frequency to 500 kHz.

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Table 1. Resistor and Switching Frequency

RESISTOR (R_{RF}) CONNECTIONS		SWITCHING FREQUENCY (f_{SW}) (kHz)
VALUE (kΩ)	CONNECT TO	
0	GND	250
187	GND	300
619	GND	400
OPEN	n/a	500
866	VREG	600
309	VREG	750
124	VREG	850
0	VREG	970

The off-time is modulated by a PWM comparator. The VFB node voltage (the mid-point of resistor divider) is compared to the internal 0.6-V reference voltage added with a ramp signal. When both signals match, the PWM comparator asserts a set signal to terminate the off time (turn off the low-side MOSFET and turn on high-side MOSFET). The set signal is valid if the inductor current level is below the OCP threshold, otherwise the off time is extended until the current level falls below the threshold.

The waveforms shown in Figure 31 show on-time control without ramp compensation. The waveforms shown in Figure 32 show on-time control without ramp compensation.

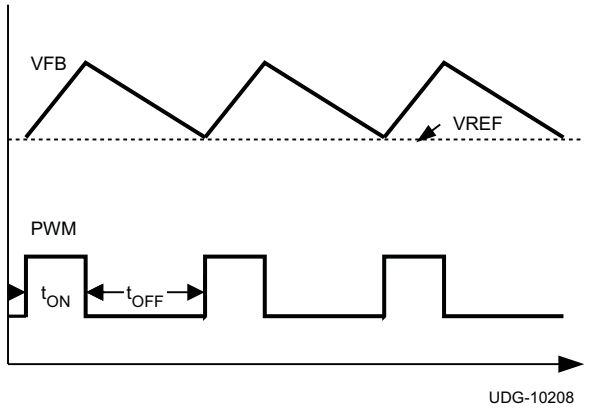

Figure 31. On-Time Control Without Ramp Compensation

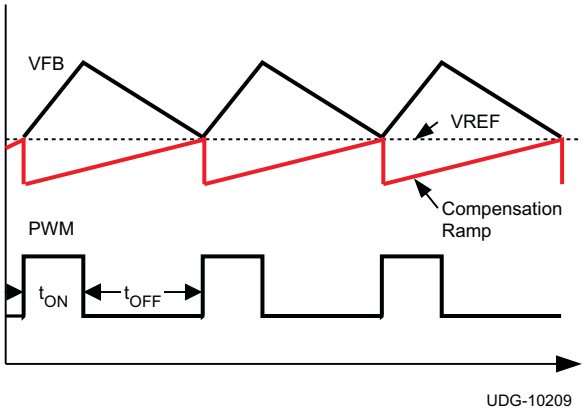

Figure 32. On-Time Control With Ramp Compensation

8.3.3 Ramp Signal

The TPS53318 and TPS53319 devices add a ramp signal to the 0.6-V reference in order to improve jitter performance. As described in the previous section, the feedback voltage is compared with the reference information to keep the output voltage in regulation. By adding a small ramp signal to the reference, the signal-to-noise ratio at the onset of a new switching cycle is improved. Therefore the operation becomes less jittery and more stable. The ramp signal is controlled to start with –7 mV at the beginning of an on-cycle and becomes 0 mV at the end of an off-cycle in steady state.

During skip mode operation, under discontinuous conduction mode (DCM), the switching frequency is lower than the nominal frequency and the off-time is longer than the off-time in CCM. Because of the longer off-time, the ramp signal extends after crossing 0 mV. However, it is clamped at 3 mV to minimize the DC offset.

8.3.4 Adaptive Zero Crossing

The TPS53318 and TPS53319 devices have an adaptive zero crossing circuit which performs optimization of the zero inductor current detection at skip mode operation. This function pursues ideal low-side MOSFET turning off timing and compensates inherent offset voltage of the Z-C comparator and delay time of the Z-C detection circuit. It prevents SW-node swing-up caused by too late detection and minimizes diode conduction period caused by too early detection. As a result, better light load efficiency is delivered.

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8.3.5 Output Discharge Control

When the EN pin becomes low, the TPS53318 and TPS53319 devices discharge the output capacitor using the internal MOSFET connected between the SW pin and the PGND pin while the high-side and low-side MOSFETs are maintained in the OFF state. The typical discharge resistance is 75 Ω. The soft discharge occurs only as EN becomes low. The discharge circuit is powered by VDD. While VDD remains high, the discharge circuit remains active.

8.3.6 Power-Good

The TPS53318 and TPS53319 devices have power-good output that indicates high when switcher output is within the target. The power-good function is activated after soft-start has finished. If the output voltage becomes within +10% and –5% of the target value, internal comparators detect power-good state and the power-good signal becomes high after a 1-ms internal delay. If the output voltage goes outside of +15% or –10% of the target value, the power-good signal becomes low after two microsecond (2-µs) internal delay. The power-good output is an open drain output and must be pulled up externally.

The power-good MOSFET is powered through the VDD pin. V_{VDD} must be >1 V in order to have a valid power-good logic. It is recommended to pull PGOOD up to VREG (or a voltage divided from VREG).

8.3.7 Current Sense, Overcurrent and Short Circuit Protection

The TPS53318 and TPS53319 device offer cycle-by-cycle overcurrent limiting control. The inductor current is monitored during the *OFF* state and the controller maintains the *OFF* state during the period in that the inductor current is larger than the overcurrent trip level. In order to provide both good accuracy and cost effective solution, TPS53319 device supports temperature compensated MOSFET $R_{DS(on)}$ sensing. The TRIP pin should be connected to GND through the trip voltage setting resistor, R_{TRIP}. The TRIP terminal sources current (I_{TRIP}) which is 10 µA typically at room temperature, and the trip level is set to the OCL trip voltage V_{TRIP} as shown in Equation 2.

$$V_{TRIP}\left(mV\right) = R_{TRIP}\left(k\Omega\right) \times I_{TRIP}\left(\mu A\right) \tag{2}$$

The inductor current is monitored by the LL pin. The GND pin is used as the positive current sensing node and the LL pin is used as the negative current sense node. The trip current, I_{TRIP} has a 3000ppm/°C temperature slope to compensate the temperature dependency of the $R_{DS(on)}$. For each device, I_{TRIP} is also adjusted based on the device-specific on-resistance measurement in production tests to eliminate the any OCP variation from device to device. Duty-cycle should not be over 45% in order to provide the most accurate OCP.

As the comparison is made during the *OFF* state, V_{TRIP} sets the valley level of the inductor current. Thus, the load current at the overcurrent threshold, I_{OCP}, can be calculated as shown in Equation 3.

$$I_{OCP} = \frac{V_{TRIP}}{\left(32 \times R_{DS(on)}\right)} + \frac{I_{IND(ripple)}}{2} = \frac{R_{TRIP}}{12.3 \times 10^3} + \frac{1}{2 \times L \times f_{SW}} \times \frac{\left(V_{IN} - V_{OUT}\right) \times V_{OUT}}{V_{IN}}$$

where

- R_{TRIP} is in kΩ

(3)

In an overcurrent or short-circuit condition, the current to the load exceeds the current to the output capacitor thus the output voltage tends to decrease. Eventually, it crosses the undervoltage protection threshold and shuts down. After a hiccup delay (16 ms plus 0.7 ms soft-start period), the controller restarts. If the overcurrent condition remains, the procedure is repeated and the device enters hiccup mode.

$$t_{HIC(wait)} = \left(2^n + 257\right) \times 4\,\mu s$$

where

- n = 8, 9, 10, or 11 depending on soft-start time selection

(4)

$$t_{HIC(dly)} = 7 \times \left(2^n + 257\right) \times 4\,\mu s \tag{5}$$

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Table 2. Hiccup Timing

SELECTED SOFT-START TIME (t_{SS})(ms)	HICCUP WAIT TIME ($t_{HIC(wait)}$)(ms)	HICCUP DELAY TIME ($t_{HIC(delay)}$)(ms)
0.7	2.052	14.364
1.4	3.076	21.532
2.8	5.124	35.868
5.6	9.220	64.540

For the TPS53318 device, the OCP threshold is internally clamped to 10.5 A. The recommended R_{TRIP} value for the TPS53318 device is less than 150 kΩ.

8.3.8 Overvoltage and Undervoltage Protection

The TPS53318 and TPS53319 devices monitor the resistor divided feedback voltage to detect over and under voltage. When the feedback voltage becomes lower than 70% of the target voltage, the UVP comparator output goes high and an internal UVP delay counter begins counting. After 1 ms, the device latches OFF both high-side and low-side MOSFETs drivers. The controller restarts after a hiccup delay (refer to Table 2). This function is enabled 1.5-ms after the soft-start is completed.

When the feedback voltage becomes higher than 120% of the target voltage, the OVP comparator output goes high and the circuit latches OFF the high-side MOSFET driver and latches ON the low-side MOSFET driver. The output voltage decreases. Before the latch-off action for both the high-side and low-side drivers, the output voltage must be pulled down below the UVP threshold voltage for a period of 1 ms. After the 1 ms period, the drivers are latched off.

8.3.9 Redundant Overvoltage Protection (OVP)

The TPS53318 and TPS53319 devices have a redundant input for OVP protection. The ROVP pin senses the voltage divided from output voltage and sends it to the OVP comparator. If this voltage is higher than 120% of the target voltage, the overvoltage protection engages and the low-side FET is turned on. When the output voltage is lower than the UVP threshold then the device latches off.

This redundant OVP function typically protects against a situation where the feedback loop is open or where a VFB pin short to GND exists. The ROVP pin has an internal 1.5-MΩ pull-down resistor.

ROVP PIN DESIGN NOTE

For an application that does not require a redundant OVP feature, the highly preferred design ties the ROVP pin to GND. If the application cannot allow an ROVP pin connection to GND, ensure that the design minimizes any potential noise injection to the ROVP pin at all cost.

8.3.10 UVLO Protection

The TPS53318 and TPS53319 devices use VREG undervoltage lockout protection (UVLO). When the VREG voltage is lower than 3.95 V, the device shuts off. When the VREG voltage is higher than 4.2 V, the device restarts. This is a non-latch protection.

8.3.11 Thermal Shutdown

The TPS53318 and TPS53319 devices monitor the internal die temperature. If the temperature exceeds the threshold value (typically 145°C), the device shuts down. When the temperature falls about 10°C below the threshold value, the device will turn back on. This is a non-latch protection.

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8.3.12 Small Signal Model

From small-signal loop analysis, a buck converter using D-CAP™ mode can be simplified as shown in Figure 33.

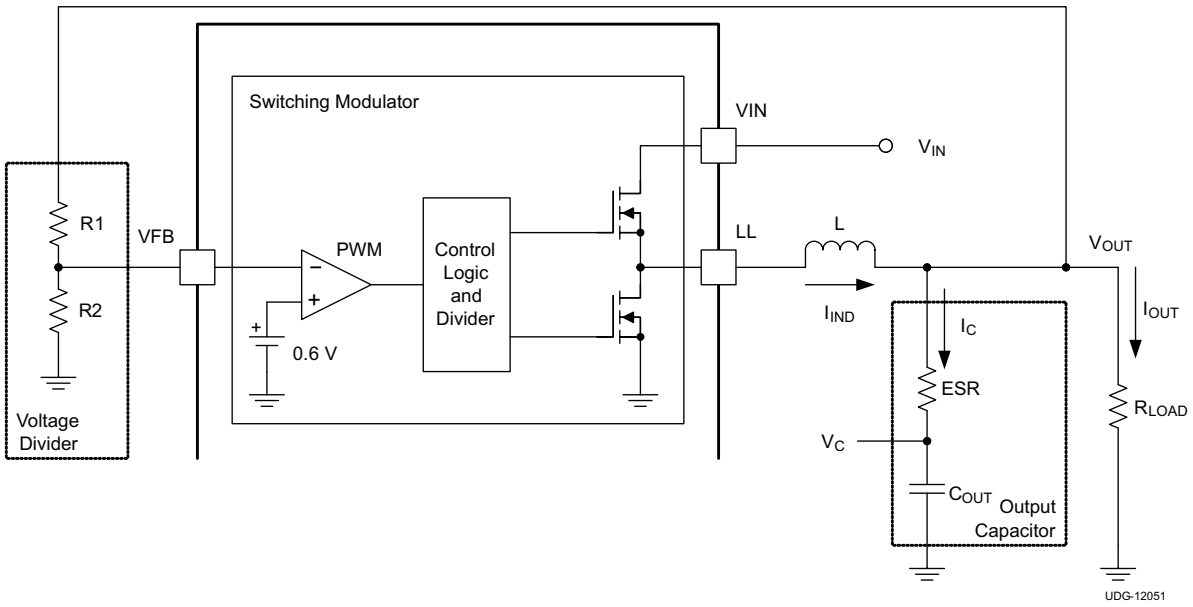

Figure 33. Simplified Modulator Model

The output voltage is compared with the internal reference voltage (ramp signal is ignored here for simplicity). The PWM comparator determines the timing to turn on the high-side MOSFET. The gain and speed of the comparator can be assumed high enough to keep the voltage at the beginning of each on cycle substantially constant.

$$H(s) = \frac{1}{s \times ESR \times C_{OUT}} \tag{6}$$

For loop stability, the 0-dB frequency, f_0, defined below need to be lower than 1/4 of the switching frequency.

$$f_0 = \frac{1}{2\pi \times ESR \times C_{OUT}} \le \frac{f_{SW}}{4} \tag{7}$$

According to the equation above, the loop stability of D-CAP™ mode modulator is mainly determined by the capacitor's chemistry. For example, specialty polymer capacitors (SP-CAP) have an output capacitance in the order of several 100 µF and ESR in range of 10 mΩ. These makes f_0 on the order of 100 kHz or less, creating a stable loop. However, ceramic capacitors have an f_0 at more than 700 kHz, and need special care when used with this modulator. An application circuit for ceramic capacitor is described in the *External Component Selection Using All Ceramic Output Capacitors* section.

8.3.13 External Component Selection Using All Ceramic Output Capacitors

When a ceramic output capacitor is used, the stability criteria in Equation 7 cannot be satisfied. The ripple injection approach as shown in Figure 34 is implemented to increase the ripple on the VFB pin and make the system stable. In addition to the selections made using steps 1 through step 6 in the *Detailed Design Procedure* section, the ripple injection components must be selected. The C2 value can be fixed at 1 nF. The value of C1 can be selected between 10 nF to 200 nF.

$$\frac{L \times C_{OUT}}{R7 \times C1} > N \times \frac{t_{ON}}{2} \tag{8}$$

where

- N is the coefficient to account for L and C_{OUT} variation

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N is also used to provide enough margin for stability. It is recommended N = 2 for V_{OUT} ≤ 1.8 V and N = 4 for V_{OUT} ≥ 3.3 V or when L ≤ 250 nH. The higher V_{OUT} needs a higher N value because the effective output capacitance is reduced significantly with higher DC bias. For example, a 6.3-V, 22-µF ceramic capacitor may have only 8 µF of effective capacitance when biased at 5 V.

Because the VFB pin voltage is regulated at the valley, the increased ripple on the VFB pin causes the increase of the VFB DC value. The AC ripple coupled to the VFB pin has two components, one coupled from SW node and the other coupled from the VOUT pin and they can be calculated using Equation 9 and Equation 10 when neglecting the output voltage ripple caused by equivalent series inductance (ESL).

$$V_{INJ\_SW} = \frac{V_{IN} - V_{OUT}}{R7 \times C1} \times \frac{D}{f_{SW}} \quad (9)$$

$$V_{INJ\_OUT} = ESR \times I_{IND(ripple)} + \frac{I_{IND(ripple)}}{8 \times C_{OUT} \times f_{SW}} \quad (10)$$

It is recommended that V_{INJ_SW} to be less than 50 mV. If the calculated V_{INJ_SW} is higher than 50 mV, then other parameters need to be adjusted to reduce it. For example, C_{OUT} can be increased to satisfy Equation 8 with a higher R7 value, thereby reducing V_{INJ_SW}.

The DC voltage at the VFB pin can be calculated by Equation 11:

$$V_{VFB} = 0.6 + \frac{V_{INJ\_SW} + V_{INJ\_OUT}}{2} \quad (11)$$

And the resistor divider value can be determined by Equation 12:

$$R1 = \frac{V_{OUT} - V_{VFB}}{V_{VFB}} \times R2 \quad (12)$$

8.4 Device Functional Modes

8.4.1 Enable, Soft Start, and Mode Selection

When the EN pin voltage rises above the enable threshold voltage (typically 1.3 V), the controller enters its start-up sequence. The internal LDO regulator starts immediately and regulates to 5 V at the VREG pin. The controller calibrates the switching frequency setting resistance attached to the RF pin during the first 250 µs. It then stores the switching frequency code in the internal registers. During this period, the MODE pin also senses the resistance attached to this pin and determines the soft-start time. Switching is inhibited during this phase. In the second phase, an internal DAC starts ramping up the reference voltage from 0 V to 0.6 V. Depending on the MODE pin setting, the ramping up time varies from 0.7 ms to 5.6 ms. Smooth and constant ramp-up of the output voltage is maintained during start-up regardless of load current.

NOTE

Enable voltage should not higher then VREG for 0.8 V.

Table 3. Soft-Start and MODE Settings

MODE SELECTION	ACTION	SOFT-START TIME (t_{SS}) (ms)	R_{MODE} (kΩ)
Auto Skip	Pull down to GND	0.7	39
		1.4	100
		2.8	200
		5.6	475
Forced CCM(1)	Connect to PGOOD	0.7	39
		1.4	100
		2.8	200
		5.6	475

(1) Device enters FCCM after the PGOOD pin goes high when MODE is connected to PGOOD through the resistor R_{MODE}.

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After the soft-start period begins, the MODE pin becomes the input of an internal comparator which determines auto skip or FCCM mode operation. If MODE voltage is higher than 1.3 V, the converter enters into FCCM mode. Otherwise it operates in auto skip mode at light-load condition. Typically, when FCCM mode is selected, the MODE pin connects to the PGOOD pin via the R_{MODE} resistor, so that before PGOOD goes high, the converter remains in auto skip mode.

8.4.2 Auto-Skip Eco-mode™ Light Load Operation

While R_{MODE}pulls the MODE pin low , the controller automatically reduces the switching frequency at light-load conditions to maintain high efficiency. More specifically, as the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to the point that its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The synchronous MOSFET is turned off when this zero inductor current is detected. As the load current further decreases, the converter runs into discontinuous conduction mode (DCM). The on-time is kept almost the same as it was in the continuous conduction mode so that it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. The transition point to the light-load operation $I_{OUT(LL)}$ (i.e., the threshold between continuous and discontinuous conduction mode) can be calculated as shown in Equation 13.

$$I_{OUT(LL)} = \frac{1}{2 \times L \times f_{SW}} \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}} \quad (13)$$

where

- f_{SW} is the PWM switching frequency

Switching frequency versus output current in the light-load condition is a function of L, V_{IN} and V_{OUT}, but it decreases almost proportionally to the output current from the $I_{OUT(LL)}$ given in Equation 13. For example, it is 60 kHz at $I_{OUT(LL)}$/5 if the frequency setting is 300 kHz.

8.4.3 Forced Continuous Conduction Mode

When the MODE pin is tied to PGOOD through a resistor, the controller keeps continuous conduction mode (CCM) in light load condition. In this mode, switching frequency is kept almost constant over the entire load range which is suitable for applications need tight control of the switching frequency at a cost of lower efficiency.

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPS53318 and TPS53319 devices are high-efficiency, single channel, synchronous buck converters suitable for low output voltage point-of-load applications in computing and similar digital consumer applications. The device features proprietary D-CAP™ mode control combined with an adaptive on-time architecture. This combination is ideal for building modern low duty ratio, ultra-fast load step response DC-DC converters. The output voltage ranges from 0.6 V to 5.5 V. The conversion input voltage range is from 1.5 V to 22 V and the VDD bias voltage is from 4.5 V to 25 V. The D-CAP™ mode uses the equivalent series resistance (ESR) of the output capacitor(s) to sense the device current. One advantage of this control scheme is that it does not require an external phase compensation network allowing for a simple design with a low external component count. Eight preset switching frequency values can be chosen using a resistor connected from the RF pin to ground or VREG. Adaptive on-time control tracks the preset switching frequency over a wide input and output voltage range while allowing the switching frequency to increase at the step-up of the load.

9.2 Typical Applications

9.2.1 Application Using Bulk Output Capacitors, Redundant Overvoltage Protection Function (OVP) Disabled

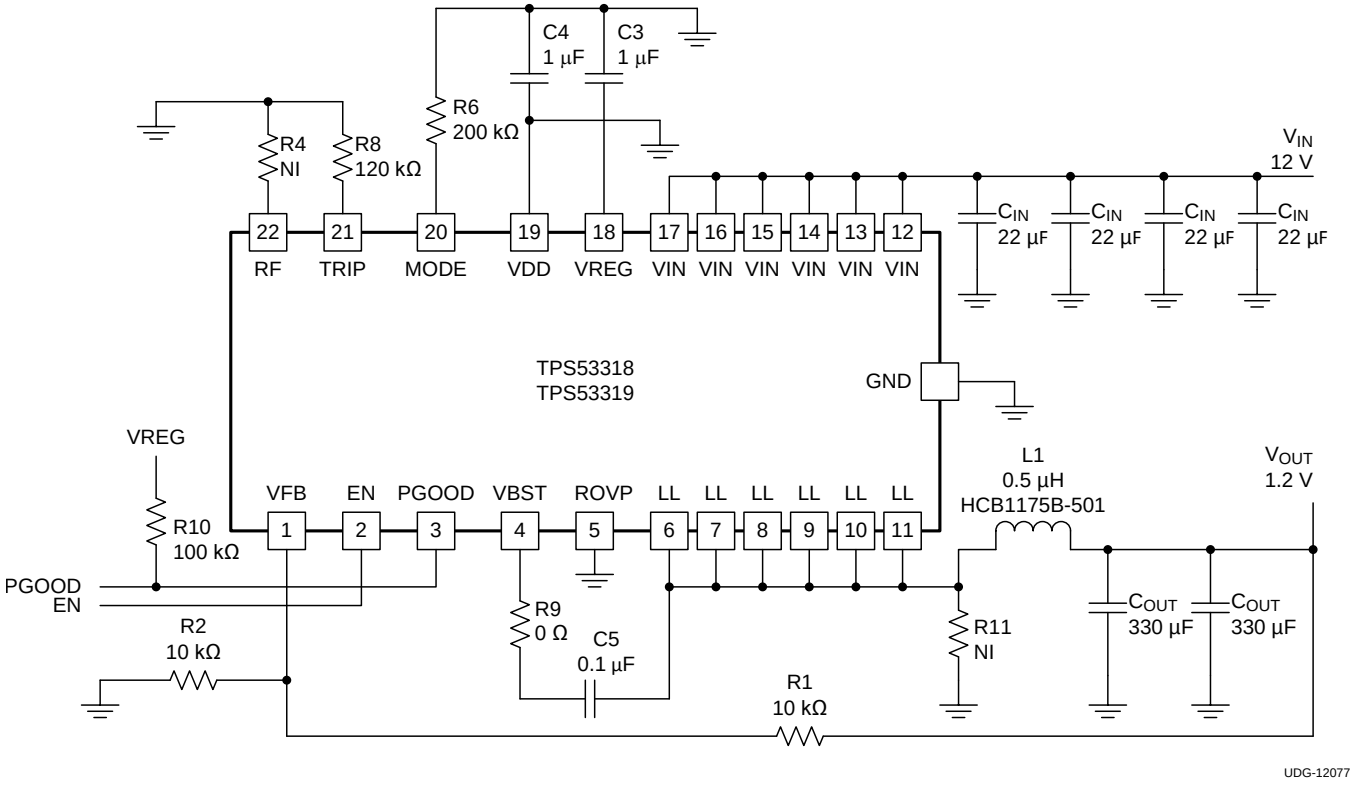

Figure 34. Typical Application Circuit, Overvoltage Protection Disabled

9.2.1.1 Design Requirements

This design uses the parameters listed in Table 4.

Typical Applications (continued)

Table 4. Design Specifications

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT CHARACTERISTICS						
V_{IN}	Voltage range		5	12	18	V
I_{MAX}	Maximum input current	V_{IN} = 5 V, I_{OUT} = 8 A		2.5		A
	No load input current	V_{IN} = 12 V, I_{OUT} = 0 A with auto-skip mode		1		mA
OUTPUT CHARACTERISTICS						
V_{OUT}	Output voltage			1.2		V
	Output voltage regulation	Line regulation, 5 V ≤ V_{IN} ≤ 14 V with FCCM		0.2%		
		Load regulation, V_{IN} = 12 V, 0 A ≤ I_{OUT} ≤ 8 A with FCCM		0.5%		
V_{RIPPLE}	Output voltage ripple	V_{IN} = 12 V, I_{OUT} = 8 A with FCCM		10		mV_{PP}
I_{LOAD}	Output load current		0		8	A
I_{OVER}	Output overcurrent			11		
t_{SS}	Soft-start time			1		ms
SYSTEMS CHARACTERISTICS						
f_{SW}	Switching frequency			500	1000	kHz
η	Peak efficiency	V_{IN} = 12 V, V_{OUT} = 1.2 V, I_{OUT} = 4 A		91%		
	Full load efficiency	V_{IN} = 12 V, V_{OUT} = 1.2 V, I_{OUT} = 8 A		91.5%		
T_A	Operating temperature			25		°C

9.2.1.2 Detailed Design Procedure

The external components selection is a simple process when using organic semiconductors or special polymer output capacitors.

9.2.1.2.1 Step One: Select Operation Mode and Soft-Start Time

Select operation mode and soft-start time using Table 3.

9.2.1.2.2 Step Two: Select Switching Frequency

Select the switching frequency from 250 kHz to 1 MHz using Table 1.

9.2.1.2.3 Step Three: Choose the Inductor

The inductance value should be determined to give the ripple current of approximately 1/4 to 1/2 of maximum output current. Larger ripple current increases output ripple voltage and improves signal-to-noise ratio and helps ensure stable operation, but increases inductor core loss. Using 1/3 ripple current to maximum output current ratio, the inductance can be determined by Equation 14.

$$L = \frac{1}{I_{IND(ripple)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}} = \frac{3}{I_{OUT(max)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}} \quad (14)$$

The inductor requires a low DCR to achieve good efficiency. It also requires enough room above peak inductor current before saturation. The peak inductor current can be estimated in Equation 15.

$$I_{IND(peak)} = \frac{V_{TRIP}}{32 \times R_{DS(on)}} + \frac{1}{L \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}} \quad (15)$$

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9.2.1.2.4 Step Four: Choose the Output Capacitor(s)

When organic semiconductor capacitor(s) or specialty polymer capacitor(s) are used, for loop stability, capacitance and ESR should satisfy Equation 7. For jitter performance, Equation 16 is a good starting point to determine ESR.

$$ESR = \frac{V_{OUT} \times 10\,mV \times (1-D)}{0.6\,V \times I_{IND(ripple)}} = \frac{10\,mV \times L \times f_{SW}}{0.6\,V} = \frac{L \times f_{SW}}{60}(\Omega) \quad (16)$$

where

- D is the duty factor.
- The required output ripple slope is approximately 10 mV per t_{SW} (switching period) in terms of VFB terminal voltage.

9.2.1.2.5 Step Five: Determine the Value of R1 and R2

The output voltage is programmed by the voltage-divider resistor, R1 and R2 shown in Figure 33. R1 is connected between VFB pin and the output, and R2 is connected between the VFB pin and GND. Recommended R2 value is from 10 kΩ to 20 kΩ. Determine R1 using Equation 17.

$$R1 = \frac{V_{OUT} - \frac{I_{IND(ripple)} \times ESR}{2} - 0.6}{0.6} \times R2 \quad (17)$$

9.2.1.2.6 Step Six: Choose the Overcurrent Setting Resistor

The overcurrent setting resistor, R_{TRIP}, can be determined by Equation 18.

$$R_{TRIP} = \left(I_{OCP} - \left(\frac{1}{2 \times L \times f_{SW}} \right) \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}} \right) \times 12.3 \quad (18)$$

where

- R_{TRIP} is in kΩ

9.2.1.3 Application Curves

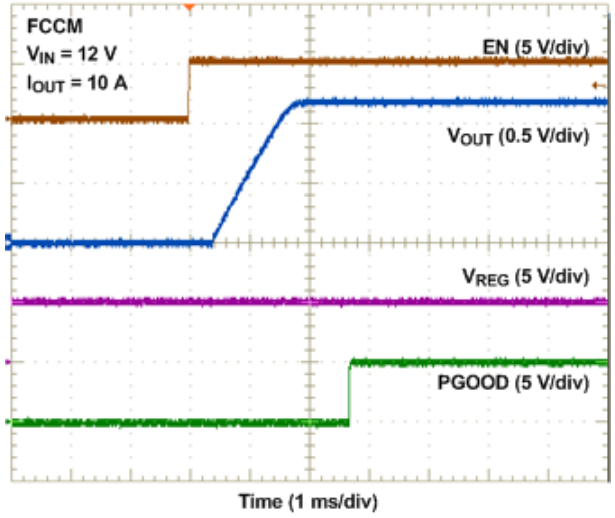

Figure 35. Start-Up

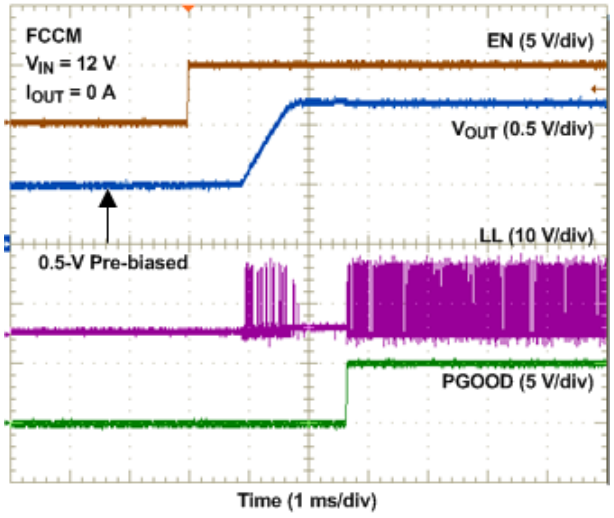

Figure 36. Pre-Bias Start-Up

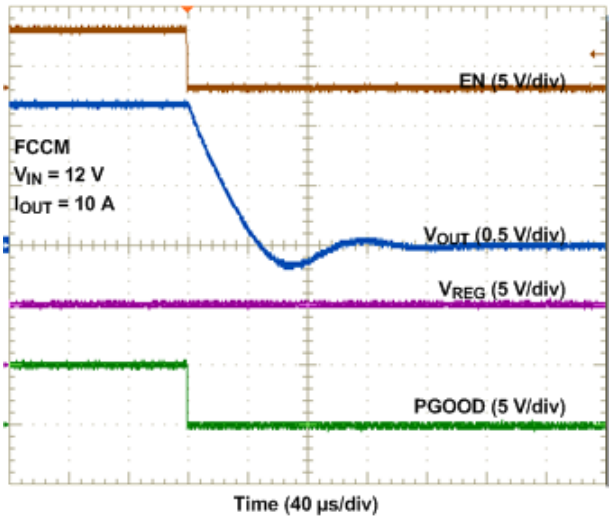

Figure 37. Shutdown

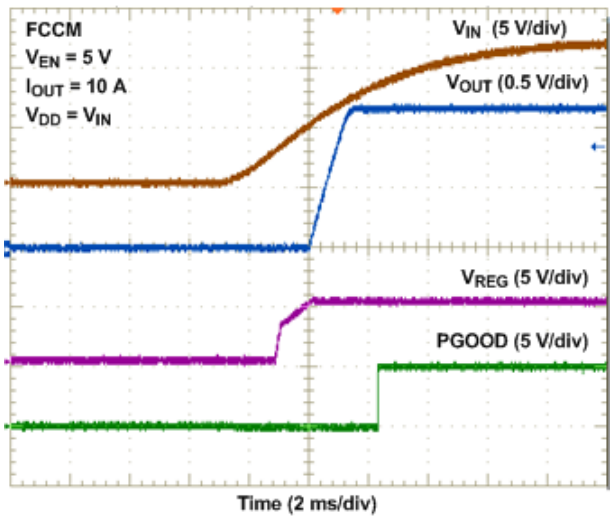

Figure 38. UVLO Start-Up

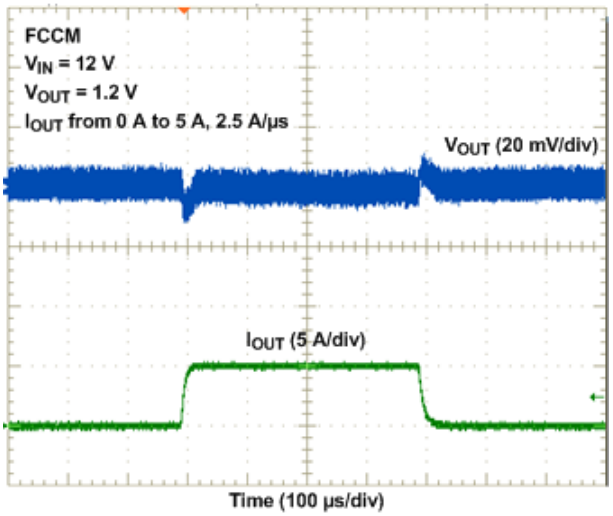

Figure 39. FCCM Load Transient

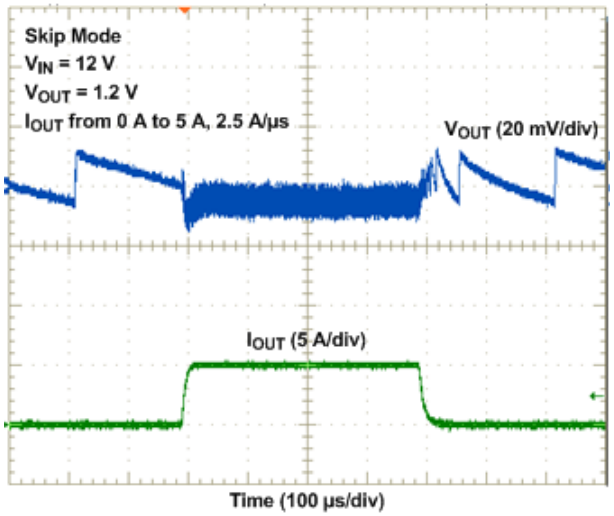

Figure 40. Skip Mode Load Transeint

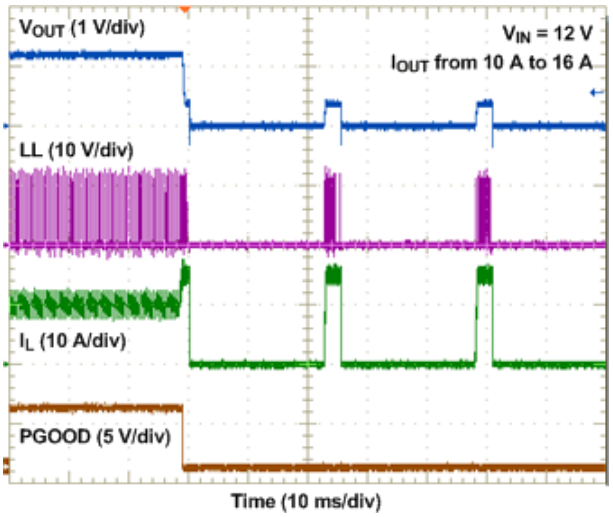

Figure 41. Overcurrent Protection

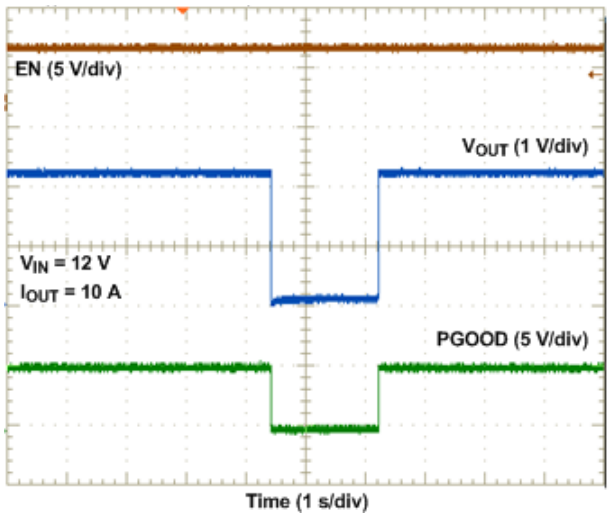

Figure 42. Over-Temperature Protection

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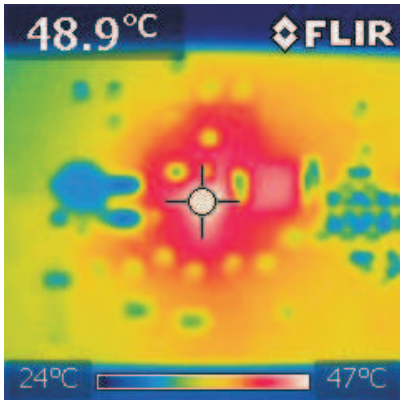
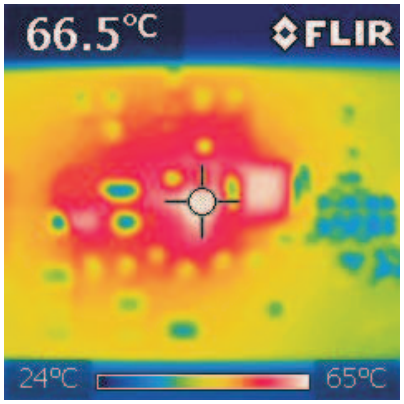


TPS53319 EVM
I_{OUT} = 14 A
V_{IN} = 12 V
f_{SW} = 500 kHz
No airflow
V_{OUT} = 1.2 V
T_A = 25°C

Figure 43. Thermal Signature



TPS53319 EVM
I_{OUT} = 14 A
V_{IN} = 12 V
f_{SW} = 500 kHz
No airflow
V_{OUT} = 5 V
T_A = 25°C

Figure 44. Thermal Signature

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9.2.2 Application Using Ceramic Output Capacitors, Redundant Overvoltage Protection Function (OVP) Enabled

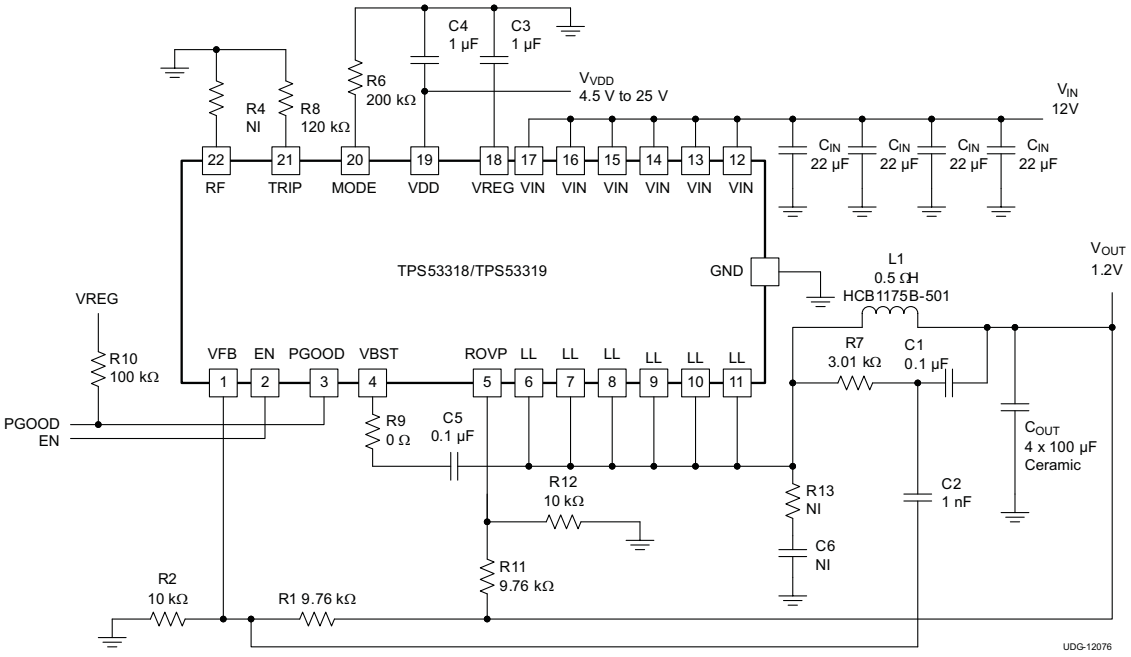

Figure 45. Typical Application Circuit, Redundent OVP Enabled

9.2.2.1 Design Requirements

This design uses the parameters listed in Table 4.

9.2.2.2 Detailed Design Procedure

The detailed design procedure for this design example is similar to the procedure for the previous design example. The differences are discussed in the following two sections.

9.2.2.2.1 External Component Selection Using All Ceramic Output Capacitors

Refer to *External Component Selection Using All Ceramic Output Capacitors* for guidelines for this design with all ceramic output capacitors.

9.2.2.2.2 Redundant Overvoltage Protection

The redundant overvoltage level is programmed according to the output voltage setting, it is controlled by resistors R11 and R12 as shown in Figure 45. Connect resistor R11 between the ROVP pin and the output, and connect resistor R12 between the ROVP pin and GND. This design recommends that the value of resistor R11 match the value of resistor R1 (or slightly higher), and that the value of resistor R2 match the value of resistor R12.

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9.2.2.3 Application Curves

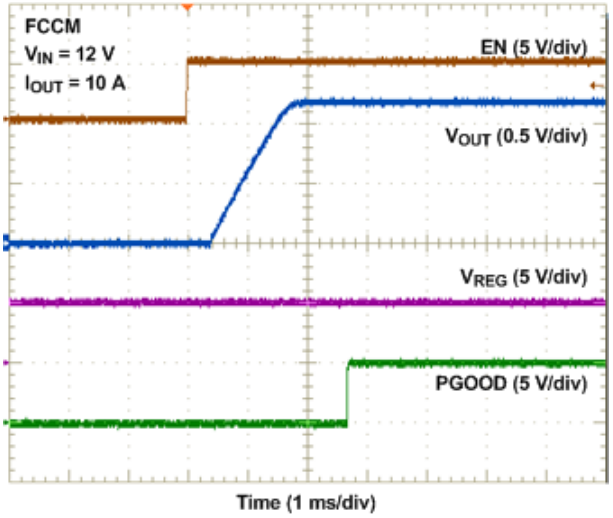

Figure 46. Start-Up

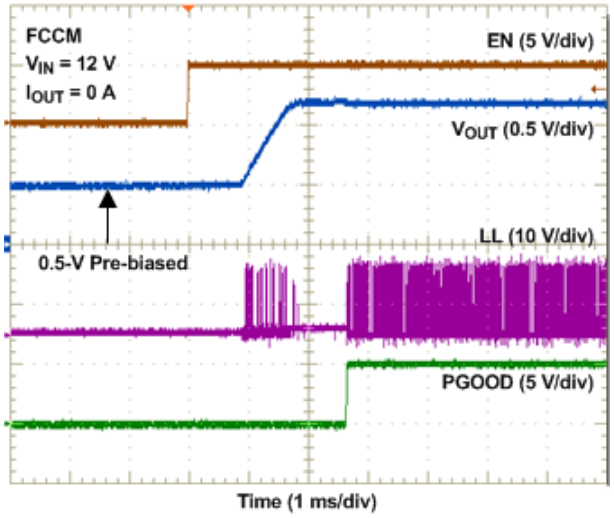

Figure 47. Pre-Bias Start-Up

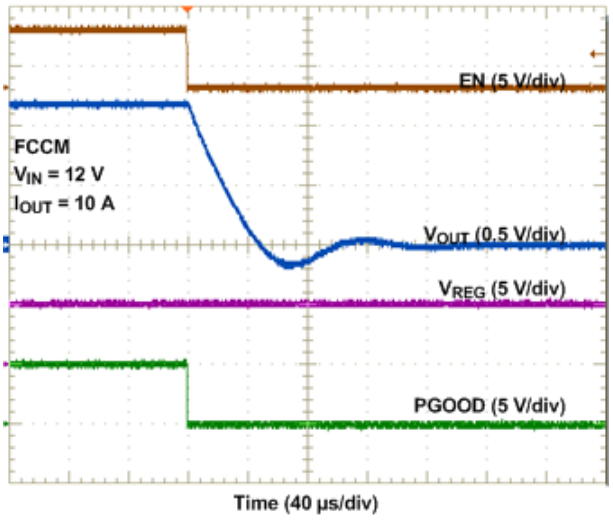

Figure 48. Shutdown

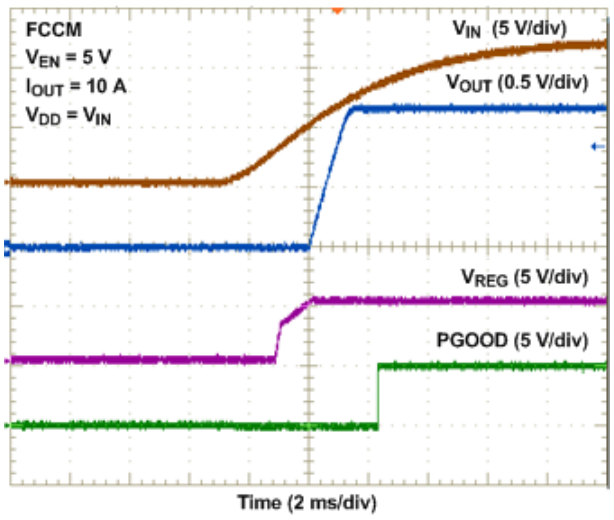

Figure 49. UVLO Start-Up

10 Power Supply Recommendations

The devices are designed to operate from an input voltage supply range between 1.5 V and 22 V (4.5 V to 25 V biased). This input supply must be well regulated. Proper bypassing of input supplies and internal regulators is also critical for noise performance, as is PCB layout and grounding scheme. See the recommendations in the *Layout* section.

11 Layout

11.1 Layout Guidelines

- The power components (including input/output capacitors, inductor and TPS53318 device or TPS53319 device) should be placed on one side of the PCB (solder side). At least one inner plane should be inserted, connected to ground, in order to shield and isolate the small signal traces from noisy power lines.
- All sensitive analog traces and components such as VFB, PGOOD, TRIP, MODE and RF should be placed away from high-voltage switching nodes such as LL, VBST to avoid coupling. Use internal layer(s) as ground

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Layout Guidelines (continued)

plane(s) and shield feedback trace from power traces and components.

- Place the VIN decoupling capacitors as close to the VIN and PGND pins as possible to minimize the input AC current loop.
- Because the TPS53319 device controls output voltage referring to voltage across VOUT capacitor, the top-side resistor of the voltage divider should be connected to the positive node of the VOUT capacitor. The GND of the bottom side resistor should be connected to the GND pad of the device. The trace from these resistors to the VFB pin should be short and thin.
- Place the frequency setting resistor (R_F), OCP setting resistor (R_{TRIP}) and mode setting resistor (R_{MODE}) as close to the device as possible. Use the common GND via to connect them to GND plane if applicable.
- Place the VDD and VREG decoupling capacitors as close to the device as possible. Ensure to provide GND vias for each decoupling capacitor and make the loop as small as possible.
- For better noise filtering on VDD, a dedicated and localized decoupling support is strongly recommended.
- The PCB trace defined as switch node, which connects the LL pins and high-voltage side of the inductor, should be as short and wide as possible.
- Connect the ripple injection V_{OUT} signal (V_{OUT} side of the C1 capacitor in Figure 45) from the terminal of ceramic output capacitor. The AC coupling capacitor (C2 in Figure 45) should be placed near the device, and R7 and C1 can be placed near the power stage.
- Use separated vias or trace to connect LL node to snubber, boot strap capacitor and ripple injection resistor. Do not combine these connections.

11.2 Layout Example

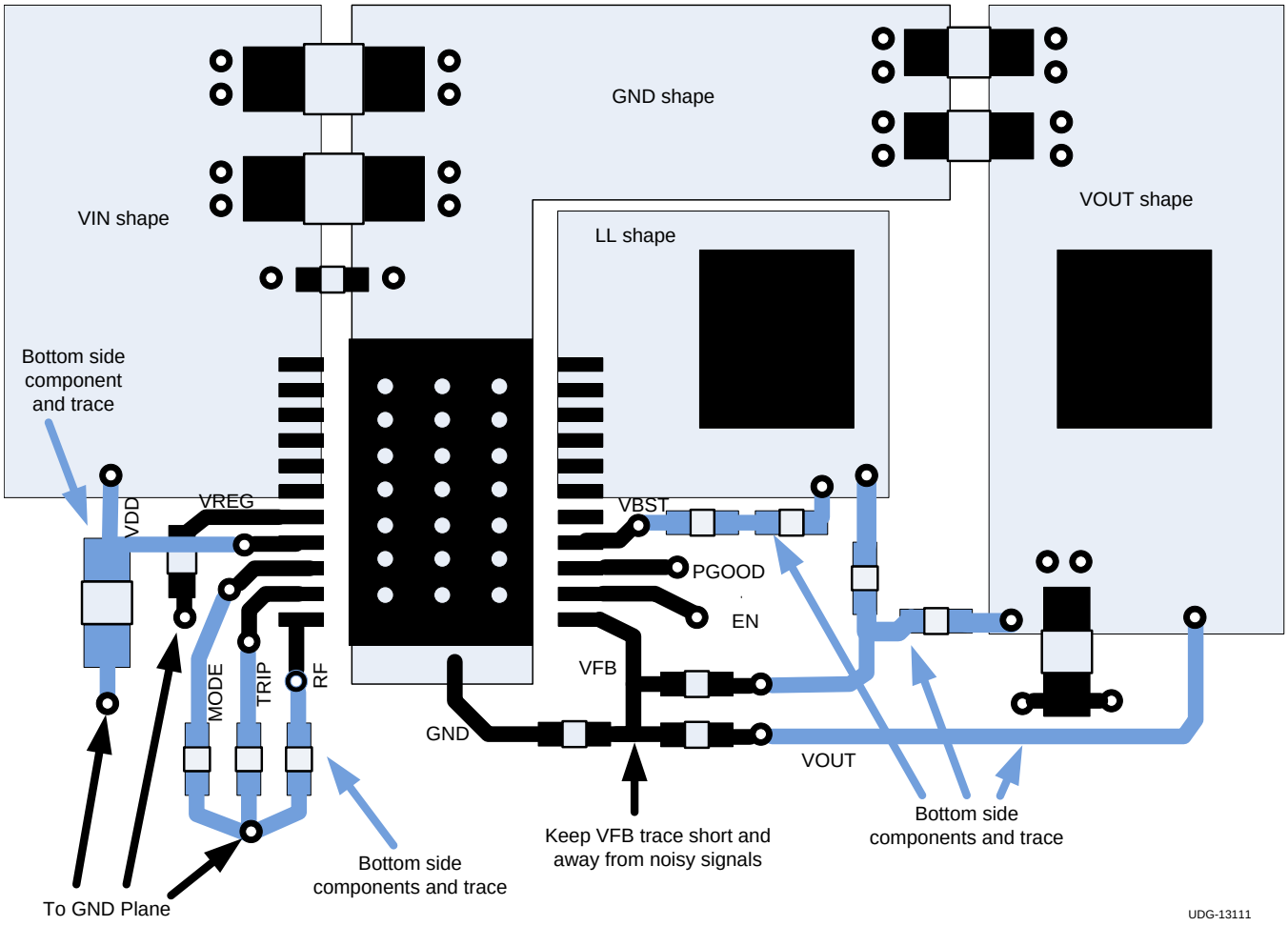

Figure 50. Layout Recommendation

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12 Device and Documentation Support

12.1 Device Support

12.1.1 Development Support

Reference Design: 7-V to 12-V Input, 1.2-V Output, 8-A Step-Down Converter for Powering Rails in Altera Arria V FPGA, PMP8824

Evaluation Module: Synchronous Switcher with Integrated MOSFETs, TPS53319EVM-136

TPS53318 TINA-TI Transient Spice Model, SLUM381

12.2 Related Links

Table 5 lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 5. Related Links

DEVICES	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TPS53318	Click here	Click here	Click here	Click here	Click here
TPS53319	Click here	Click here	Click here	Click here	Click here

12.3 Trademarks

Eco-mode, D-CAP, NexFET, PowerPAD are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS53318DQPR	ACTIVE	LSON-CLIP	DQP	22	2500	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	53318DQP	Samples
TPS53318DQPT	ACTIVE	LSON-CLIP	DQP	22	250	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	53318DQP	Samples
TPS53319DQPR	ACTIVE	LSON-CLIP	DQP	22	2500	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	53319DQP	Samples
TPS53319DQPT	ACTIVE	LSON-CLIP	DQP	22	250	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	53319DQP	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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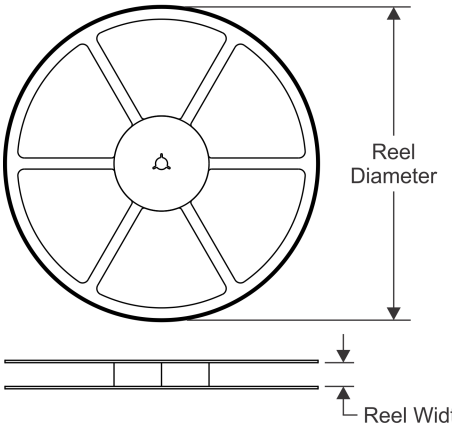
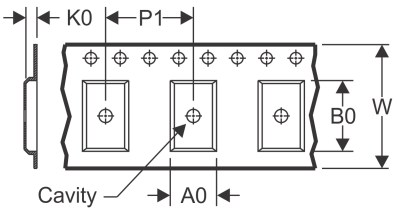
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

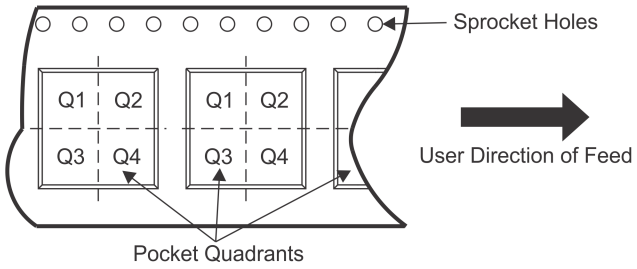


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

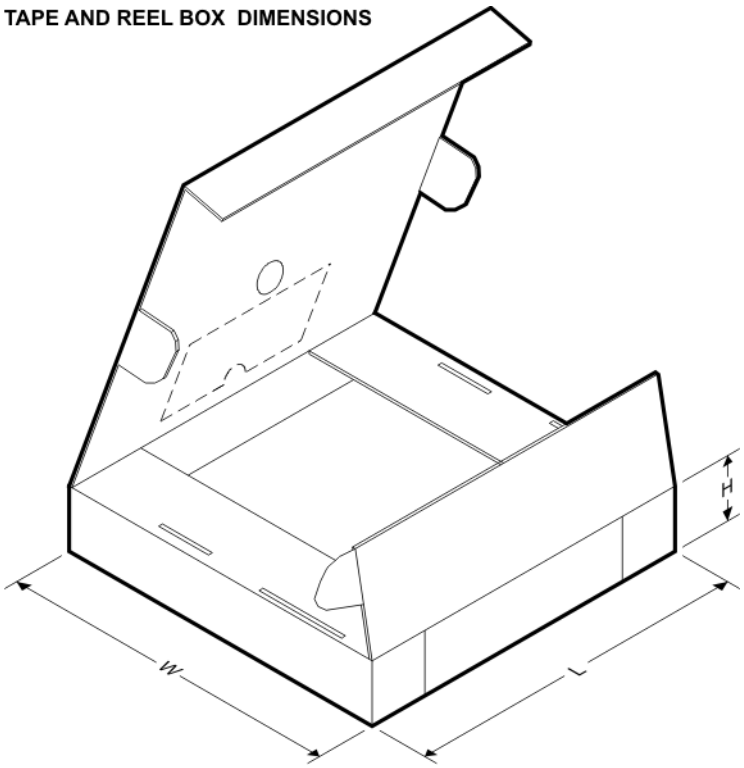
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS53318DQPR	LSON-CLIP	DQP	22	2500	330.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1
TPS53318DQPT	LSON-CLIP	DQP	22	250	180.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1
TPS53319DQPR	LSON-CLIP	DQP	22	2500	330.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1
TPS53319DQPT	LSON-CLIP	DQP	22	250	180.0	12.4	5.3	6.3	1.8	8.0	12.0	Q1

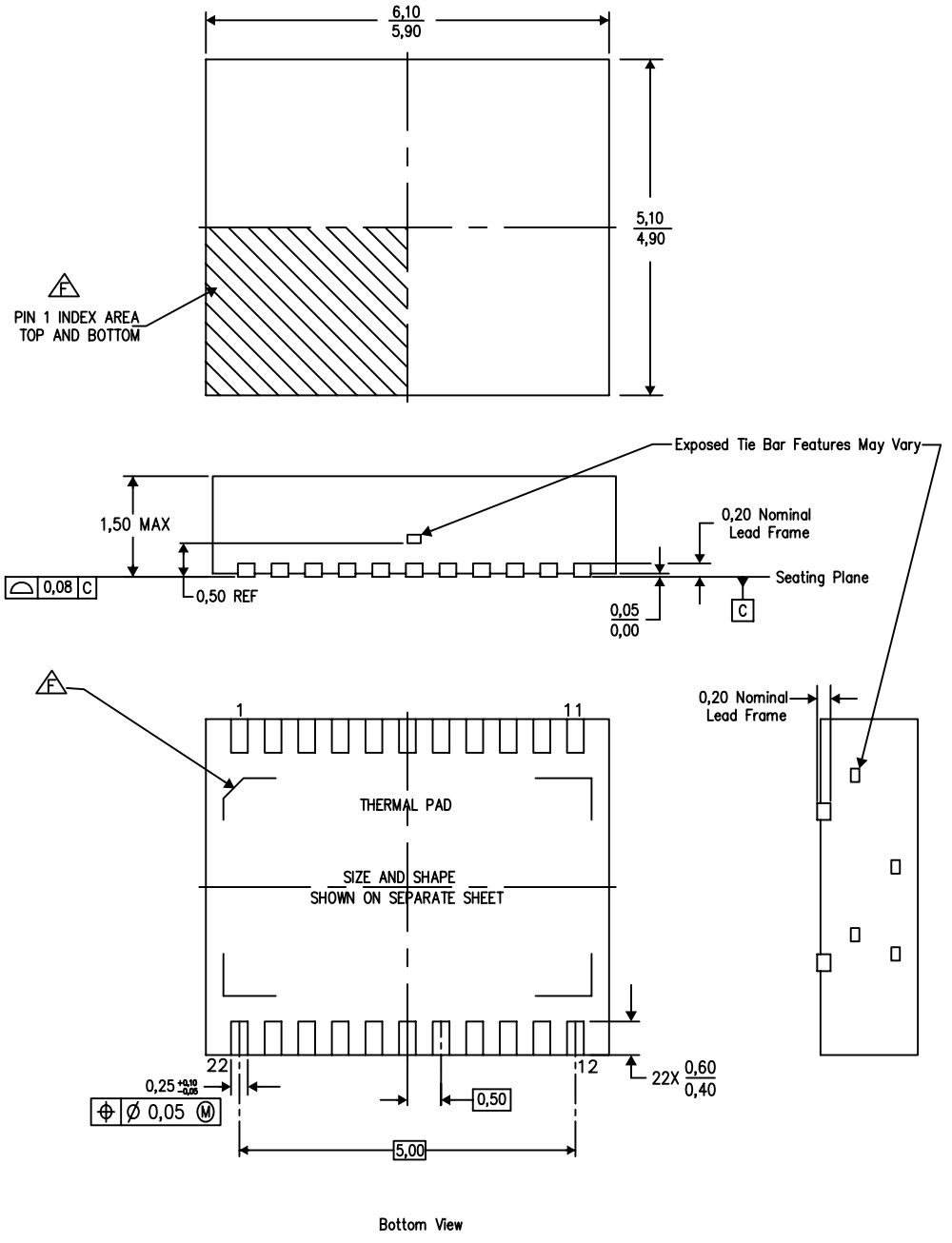
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS53318DQPR	LSON-CLIP	DQP	22	2500	367.0	367.0	35.0
TPS53318DQPT	LSON-CLIP	DQP	22	250	210.0	185.0	35.0
TPS53319DQPR	LSON-CLIP	DQP	22	2500	367.0	367.0	35.0
TPS53319DQPT	LSON-CLIP	DQP	22	250	210.0	185.0	35.0

DQP (R–PSON–N22) PLASTIC SMALL OUTLINE NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Small Outline No–Lead (SON) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.

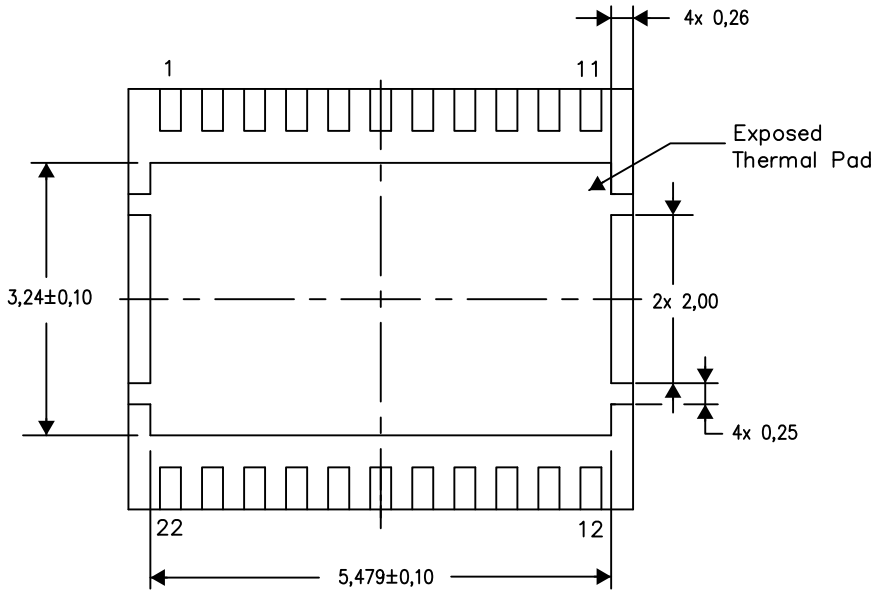
DQP (R–PSON–N22) PLASTIC SMALL OUTLINE NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



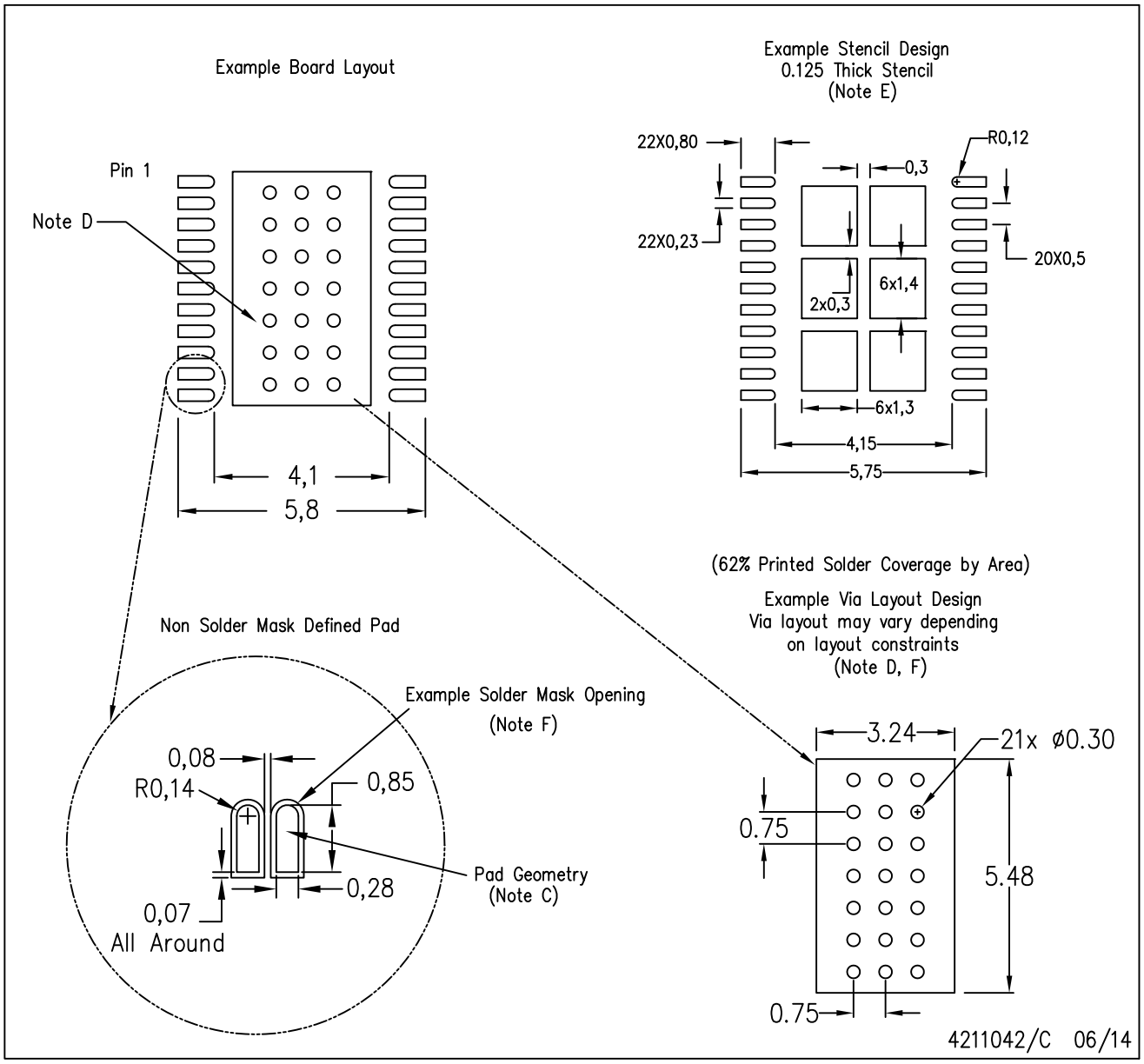
Bottom View

Exposed Thermal Pad Dimensions

4211024–3/F 06/14

NOTE: All linear dimensions are in millimeters

DQP (R–PSON–N22) PLASTIC SMALL OUTLINE NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.

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